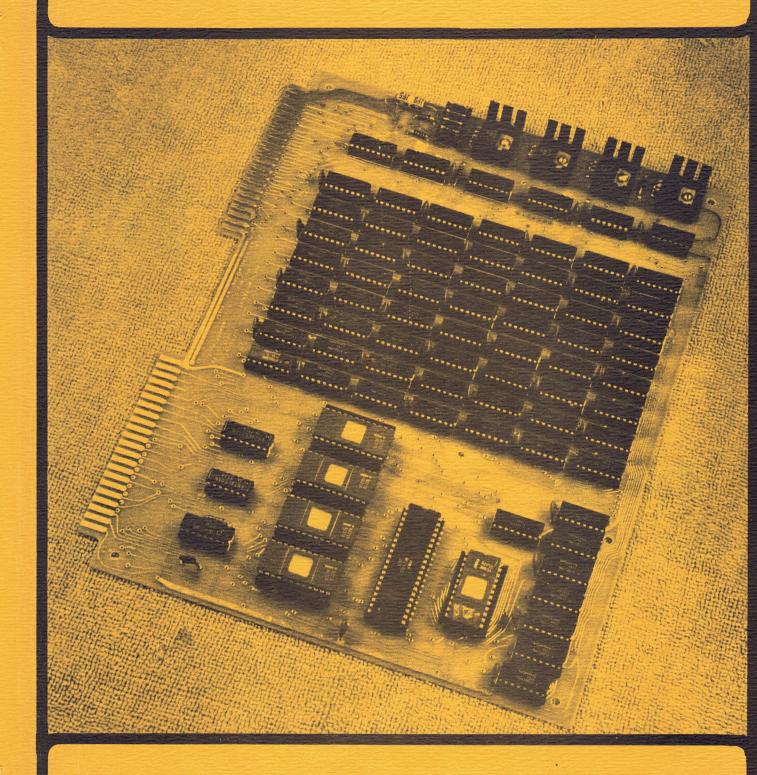
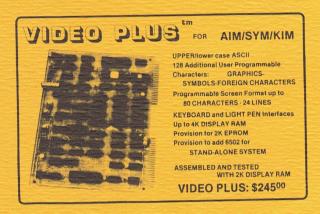
MEMORY PLUS

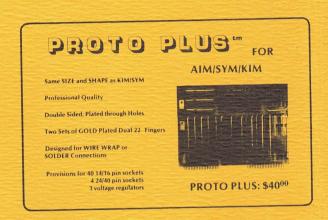


AIM - SYM - KIM

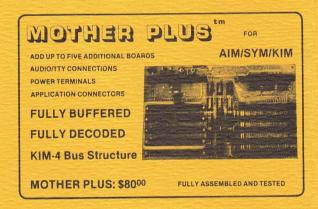
AIM/SYM/KIM USERS

Meet some other members of our 'ASK' family.









The COMPUTERIST specializes in expansion needs for your AIM/SYM/KIM. We offer a wide variety of support in expansion boards, power supplies, and software. Since we are continuously developing new 6502 based products, please contact us for the latest product and pricing information.

Prices subject to change without notice.

The COMPUTERIST, Inc. P. O. Box 3 So. Chelmsford, MA 01824 617/256-3649

[October 1979]

Table of Contents

Warranty and Service

Should you experience difficulty with your MEMORY PLUS board and be unable to diagnose or correct the problem, you may return the board to The COMPUTERIST for repair. MEMORY PLUS is warranted by The COMPUTERIST against defects in workmanship and materials for a period of ninety (90) days from date of delivery. During the warranty period, The COMPUTERIST will repair or, at its option, replace at no charge components that prove to be defective provided that the board is returned, shipping prepaid, to:

The COMPUTERIST, Inc.
Service Department
34 Chelmsford Street
Chelmsford, MA 01824

This warranty does not apply if the board has been damaged by accident or misuse, or as a result of repairs or modification made by other than authorized personnel at the above service facility. No other warranty is expressed or implied. The COMPUTERIST is not liable for consequential damages.

Beyond the ninety (90) day warranty period, MEMORY PLUS boards will be repaired for a reasonable service fee. All service work performed by The COMPUTERIST beyond the warranty period is warranted for an additional ninety (90) day period after shipment of the repaired board.

It is the customer's responsibility to return the board with shipping charges prepaid to the above service facility. For in-warranty service, the board will be returned to the customer, shipping prepaid, by the fastest economical carrier. For out-of-warranty service, the customer will pay for shipping charges both ways. The repaired board will be returned to the customer C.O.D. unless the repairs and shipping charges are prepaid by the customer.

All material in the MEMORY PLUS Manual is Copyright © 1979 by The COMPUTERIST Inc.

INTRODUCTION

MEMORY PLUStm has been designed specifically to work with the KIM-1, SYM-1, AIM 65 microcomputers. It greatly extends the power of the basic MICRO by providing four major facilities:

RAM Memory: 8K bytes of low power 2102 type static RAM.

ROM Memory: Sockets and decoding for up to 8K bytes of 2716 type erasable programmable read-only memory - EPROM

Versatile Interface Adapter: Two 8-bit programmable I/O ports with additional handshaking lines. Two sophisticated timers.

A serial-to-parallel and parallel-to-serial shift register.

EPROM Programmer: All components required to programming the INTEL type 2716 EPROM. This includes a programming socket, all hardware, a +25 volt regulator circuit, and an EPROM Programming program on cassette tape.

Other features of MEMORY PLUS include:

On board +5 volt regulators: User need only supply +8 to +10 unregulated power for running everything on MEMORY PLUS except the EPROM Programmer.

Provision for Battery Backup: External batteries may be connected to MEMORY PLUS to maintain power to the RAMs during any power outage, thereby automatically preserving the contents of the RAM.

All ICs are socketted: This means that in the event of a chip failure in the field the user may often be able to correct the problem immediately and locally, and not be required to ship the board back to the factory for service.

May be mounted directly underneath the KIM-1 or SYM-1. Mounting holes are provided so that the board may be attached to the existing holes on the KIM-1 or SYM-1.

Compatible with the KIM-4 Bus: The basic connections between the MICRO and MEMORY PLUS are identical to those between the KIM-1 and KIM-2/KIM-3. Therefore, users who have already designed and/or built systems based on these KIM boards may easily adapt to the MEMORY PLUS board.

Provision for Off-the-board EPROM Programming Socket: All of the lines necessary to add an external EPROM Programming Socket are available at the MEMORY PLUS application connector.

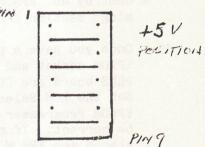
Fully Assembled, Burned-in, and Tested: Ready to go.

Switch Selectable Addressing: Starting address for RAM and ROM are set by rotary switches on the board. They may each start at any 8K boundary (2K hex).

The quickest way to get your new MEMORY PLUS board "up and running" with your MICRO is to take your time and follow all of the steps outlined below.

- 1. Carefully unpack your MEMORY PLUS board from its individual box, padding, and protective anti-static wrapping. While none of the components on this board are unusually susceptible to static, any chip can be damaged (destroyed) by a large static shock. So, take some care about avoiding static buildup.
- 2. Examine the board for any visible damage which may have occurred in shipping. Push all IC's firmly into their sockets. Unbend any capacitors which have been bent.
- 3. Read briefly the entire MEMORY PLUS manual. Pay particular attention to the main sections on "POWER", "RAM Memory", "EPROM Memory", and "VERSATILE INTERFACE ADAPTER", but do not try to memorize everything.
- 4. Build the required connector cables following the wiring list labelled "MEMORY PLUS to MICRO Connections".
- 4A <u>KIM-1 ONLY</u>; If you are only planning to use the RAM memory to start, then only the expansion connector cable is required. A wire running from pin E-16 of MP to A-K of KIM for the DECODE. Remember to remove the wire you currently have between pin A-K of KIM and pin A-1 of KIM which grounds the DECODE signal for an unexpanded system.
- 5. Carefully check the cable you built for any errors or bad connections.
- 6. Set up your power for MEMORY PLUS in one of the following ways:
 - a. If you have a single +5V supply which is going to run both the MICRO and MEMORY PLUS (it must be capable of about 3.5 amps), then the following connections should be made:

MP E-21 to MICRO E-21
MP E-Y to MICRO E-21
MP A-A to MICRO A-A



The Header should be positioned with no wire near the edge of the board.

- b. If you have a separate +5 regulated supply for MEMORY PLUS, the above connections must <u>not</u> be made. The header should be positioned with no wire near the edge of the board. Attach supply to MP E-21/E-Y.
- c. If you have a +8 to +10 unregulated supply, then the above connections must \underline{not} be made. The header should be positioned with a wire near the edge of the board. Attach supply to MP E-19/E-20.
- 7. Connect the MICRO and MEMORY PLUS together via the cables you have made.
- 8. Set the RAM Select Switch to the 2000 position.

- 9. Turn on the power supply. Using the MICRO monitor, examine and modify a few RAM locations to verify that they basically work. With the RAM switch set to 2000, locations 2000 through 3FFF are accessible. If you are unable to examine and modify these locations, then check steps 2 to 8 for any errors. If you can not find anything you did wrong, then go to the section on "MEMORY PLUS Testing and Field Repair" on page 16.
- 10. If the above preliminary examination of RAM memory is successful, then you are ready to run a more rigorous memory test. Follow the instructions in the section on "RAM Memory Test". If these tests work, and all you plan to use on MEMORY PLUS is the RAM, then you are done with the initial set up and check out.
- 11. If you plan to use the EPROM Programmer, you must build the cable that goes between the MICRO and MEMORY PLUS application connectors if you have not already done so. Follow the wiring list labelled "MEMORY PLUS to MICRO Connections". Carefully check the cable you built and review the power connections as discussed in step 6 above.
- 12. Connect the MICRO and MEMORY PLUS together with the application cable.
- 13. No specific tests are provided for testing the VIA. If you wish to test this chip, read the section on "VERSATILE INTERFACE ADAPTER" and the "MCS6522 VERSATILE INTERFACE ADAPTER Data Sheet" contained in your MICRO Manual. You may then devise your own tests dependent on how you intend to use the VIA chip.
- 14. The only simple way to test the EPROM Programmer is to program an EPROM. The EPROM Programmer requires a +25 volts at 30 milliamps. The best way to provide this is by using the on board regulator circuit. A +27 to +30V unregulated supply can be connected to pin E-3 of the MEMORY PLUS expansion connector. See the section on "EPROM Programming" for details. This will provide about +24.7V for EPROM programming and will prevent over voltages which can destroy an EPROM. Follow the instructions in the "EPROM Programming" section and program an EPROM.
- 15. Once you have a programmed EPROM, you can place it into the correct EPROM socket and try to use it. The "standard" addresses for the MEMORY PLUS board are COOO C7FF, C800 CFFF, D000 D7FF, and D800 DFFF. Set the ROM Select Switch to the desired 8K starting address. Since the EPROM Programmer Program verified as it programmed, the contents should be correct. If not, then there is probably a problem in where you have placed the EPROM (wrong socket) or which direction you have inserted the EPROM (pin 1 goes upper right corner). If the contents of the EPROM look okay, then execute the code to determine if it runs correctly. If the code looks correct, then it should run properly.
- 16. Congratulations. You now have an expanded MICRO system with a lot of new capabilities. You should now make yourself more familiar with the MEMORY PLUS facilities by re-reading the documentation, particularly the VIA Data Sheet.

MEMORY PLUS to MICRO Connections

		MEMORY PLUS	MICRO	Expansion	Connector	MEMORY PLUS	MICRO
	Function	Pin#	Pin#		Function	Pin#	Pin#
	Ground	E-1	E-22		Ground	E-A	E-22
*	+5V Battery	E-2		1 -	ABO	E-B	E-A
*	+27 Unreg.	E-3		green/wit	AB1	E-C	E-B
	IRQ	E-4	E-4		AB2	E-D	E-C
	1114	E-5			AB3	E-E	E-D
		E-6			AB4	E-F	E-E
	RST	E-7	E-7		AB5	E-H	E-F
	DB7	E-8	E-8		AB6	E-J	E-H
	DB6	E-9	E-9		AB7	E-K	E-J
	DB5	E-10	E-10		AB8	E-L	E-K
	DB4	E-11	E-11		AB9	E-M	E-L
	DB3	E-12	E-12		AB10	E-N	E-M
	DB2	E-13	E-13		AB11	E-P	E-N
	DB1	E-14	E-14		AB12	E-R	E-P
	DBO	E-15	E-15		AB13	E-S	E-R
	DECODE	E-16	A-K		AB14	E-T	E-S
		E-17	A-K		AB15	E-U-	E-T
		E-18			Phase 2	E-V	E-U
	+8V Unreg.	E-19		Blaun	Read/Write	E-W	E-V
	+8V Unreg.	E-20			Phase 2	E-X	E-Y
	+5V Regulated		E-21	roon .	+5V Regulated		E-21
	Ground	E-22	E-22	ZWART	Ground	E-Z	E-22
		MEMORY PLUS	MICRO	Application	on Connector	MEMORY PLUS	MICRO
	Function	Pin#	Pin#		Function	Pin#	Pin#
	Ground	A-1	A-1		+5V Regulated	A-A	A-A
	MPA1	A-2			MPB6	A-B	
	MPA2	A-3				A-C	
	MPA3	A-4				A-D	
	MPA4	A-5			MCA 2	A-E	
	MPA5	A-6			MCA.	A-F	
	MPA6	A-7			MCB1	A-H	
	MPA7	A-8			MCB2	A-J	te bonce
	MPB0	A-9			DECODE	A-K	A-K
	MPB1	A-10	Lat. State 1			A-L	
	MPB2	A-11	-X SEE	IMPERTHAT	WAZNING	A-M	
	MPB3	A-12	NOTE	ON PACE 12	ABOUT .	A-N	
	MPB4	A-13	F-2	/E-3 CONN	IGO TOUR	A-P	
	MPAO	A-14	TO LUEN	12-3 001111		A-R	
	MPB7	A-15				A-S	
	MPB5	A-16				A-T	
	MCB2	A-17				A-U	
	1) () A ()	A-18				A-V	
	PRA8	A-19	A-9			A-W	
	PRA9	A-20	A-10			A-X	
	PRA10 +25V Regulated	A-21	A-11			A-Y	
	+COV REBUIATE	1 H-CC				A-Z	

^{*} One of the two DECODE lines must be connected to the KIM-1. This is not required on the SYM-1 or AIM 65.

The power requirements for MEMORY PLUS are simple and on-board regulators are provided to make powering the board even easier. Essentially the board requires only +5 volts at about 2.0 amps. While the actual current requirements will vary slightly with the particular components on any board, the table below shows the individual and collective power requirements.

Component	#	T	ypical	Ma	ximum	Measured	Max Total	Meas.	Total
74LS00 74LS04	1				8	3	8	3 4	
74LS32 74LS138	1 3		5		10	6	10 30	18	
74LS367	3		14		24	17	72	51	
2716	4		57	1	05	45	420	180	
6522 M-1	1		50	[A]	60	52	60	52	
2102L [B]	32		14		22	14	704	448	
2102L 4-8	32		14		22	14	704	448	
Total System							2016	1206	[C]

Notes: All current values in milliamps.

- [A] Value as estimated by an engineer at MOS Technology.
- [B] 2102Ls are split into two sections of 4K RAM each in the table for purposes of discussion below.
- [C] Measurements were taken with an inexpensive meter and should be only used as a guide to the system current requirements.
- [D] The above values were obtained with Fairchild 21L02s. The values may vary with other 21L02s produced by other manufacturers and supplied with your MEMORY PLUS board.

Regulated +5 Volt Supply. If the MEMORY PLUS is to be powered by regulated +5 volts, then the supply should be connected to pins E-21 and E-Y on the MEMORY PLUS expansion connector. The supply should be capable of supplying at least 2.0 amps in addition to any other board it is driving such as the KIM-1. The Header at the top of the board should be positioned so that the bus wires are away from the top of the board and the Header notched corner is positioned at pin 9.

Unregulated +8 to +10 Volt Supply. If the MEMORY PLUS is to be powered by unregulated +8 to +10 volts, then the supply should be connected to pins E-19 and E-20 on the MEMORY PLUS expansion connector. The supply should be capable of supplying at least 2.5 amps. This supply is distributed to three +5 volt regulators which each handle a separate section of the board.

Regulator Q4 supplies the high 4K of 2102L RAM with 448 to 704 milliamps.

Regulator Q5 supplies all support chips, the 2716s and the 6522 with 310 to 608 milliamps.

Regulator Q6 supplies the low 4K of 2102L RAM with 448 to 704 milliamps.

The Header at the top of the board should be positioned so that the bus wires are near the top of the board and the Header notched corner is positioned at pin 1.

The only other power requirement for the MEMORY PLUS board is +25 volts at 30 milliamps during programming of an EPROM. This voltage may be provided as either regulated +25 volt or unregulated +28 to +30 volts.

Regulated +25 Volt Supply. Programming of the INTEL 2716 EPROM requires +25V. This may be attached to pin A-22 of the MEMORY PLUS application connector. Care must be taken to assure that the voltage is within the limits of +24 to +26 volts. A higher voltage will destroy the EPROM as both the INTEL documentation and my own personal experience can attest.

- Unregulated +27 to +30 Volt Supply. MEMORY PLUS provides a circuit with a +24 volt regulator and a diode to produce a regulated +24.7 volts from an unregulated +27 to +30 volt supply. The unregulated supply, which may be three +9 volt transistor radio type batteries, is attached to pin E-3 of the MEMORY PLUS expansion connector. Since the programming voltage is so critical and since an over voltage can destroy an EPROM, use of this on board regulator is recommended. The three battery clips provided in the Accessory Bag are for the purpose of hooking up three +9 volt batteries.
- * Battery Backup. Since it is often desirable to be able to protect the contents of the RAM memory during a transient power interruption, or for longer periods of time, a provision has been made for battery backup to be connected to the MEMORY PLUS board. The batteries must be capable of providing between about 3.5 and 4.5 volts. They are connected to pin E-2 of the MEMORY PLUS expansion connector. There are diodes in the circuit which prevent current from being drawn from the batteries during normal system functioning. When the power drops, however, the batteries will automatically start supplying the required current. The amount of current will depend on the basic system configuration. If the MEMORY PLUS board is being run from +5 volts, then the batteries must supply the entire board. If the board is being run from the +8 to +10 volt regulators, then the battery backup will only run the RAM memory chips. This will result in a lower current drain on the batteries. The length of time that the system will retain its RAM contents on battery power will be a function of the configuration and the capacity of the batteries.

* SER IMPORTANT WARRING NOTE ON PAGE 18.

Cassette Loading Instructions

The cassette tape is recorded in standard KIM format at the normal rate. The programs have been written so that they will run on a KIM-1, SYM-1 or AIM 65 with no modification.

The MEMORY TEST is the first program on the tape. It has program ID = 10. It loads into locations 0000 through 00D8. It is set up to test memory from 2000 to 3FFF. The starting address of the program is 0002. See pages 21 to 23 of this manual for the MEMORY TEST Source Listing and page 20 for instructions on using the program.

The PROM PROGRAMMER is the second program on the tape. It has Program ID = 20. It loads into locations 0000 through 00E7. The programming parameters must be set up in locations 0000 through 0005 as outlined in the section on EPROM Programming, pages 11 to 13. The starting address of the program is 0011. Complete Source Listings are located on pages 14 through 16 of this manual.

RAM Memory

The Random Access Memory (RAM) used with MEMORY PLUS is 2102-type static RAM. Each 2102 chip contains 1024 bits of memory. Any single bit is directly addressable. By addressing eight chips in parallel, an eight bit word is accessed. It takes eight 2102 chips to provide 1024 8-bit bytes. The MEMORY PLUS provides 8K bytes of 8-bit RAM (actually 8192 bytes). This requires 64 2102 chips: eight chips per 1K times eight K.

The 2102 chips used with MEMORY PLUS are Synertek 21L02B or equivalent. This version of 2102 has the following basic parameters:

SPEED: 450 nanosecond access time

POWER: 30 milliamp worst case (these are "low power" chips)

single +5 voltage required

The MEMORY PLUS RAM is organized into a single contiguous 8K block of memory. The location of the RAM in the MICRO addressing space is defined by a switch which may be set to start at any 8K boundary (2K hex boundary). Looking at the board with the regulators at the top, the RAM select switch is the left switch of the pair of rotary switches. Using the flat side of the switch as the position indicator, the addresses are set as follows:

		4			4	
	6		2	E		6
On-board Address Select Switches for RAM and ROM	8	RAM	Not	Selected	ROM	8
	A	С	E	2	С	A

The address associated with each position is:

2K 4K	2000			Assumed as the RAM address in this manual.
6K	6000	to	7FFF	
8K	8000	to	9FFF	
AK	A000	to	BFFF	
CK	C000	to	DFFF	Assumed as the ROM address in this manual.
EK	E000			Not normally used for RAM since interrupt vectors must be defined in FFFA to FFFF if this memory is
				addressed. See note in EPROM Memory about using this space for EPROM.

The exact layout of the individual RAM chips may be found in a diagram in the section on "MEMORY PLUS Testing and Field Repair".

EPROM Memory

The Erasable Programmable Read-Only Memory (EPROM) used with MEMORY PLUS is an ultraviolet erasable and electrically programmable 2716 type ROM. This is a fairly new memory chip. The version used in MEMORY PLUS is made by INTEL. It is not compatible with the 2716 made by some other manufacturers such as Texas Instruments. It may be second sourced by other manufacturers, but be certain that any EPROM you purchase is at least INTEL 2716 compatible. Each 2716 chip contains 16,384 bits of memory. The addressing of the chip is such that data is accessed eight bits at a time. The organization is 2048 bytes of eight bits each. A single 2716 provides 2K bytes of memory. The MEMORY PLUS board has provision for up to four 2716 chips providing for a maximum of 8K bytes of EPROM.

The 2716 chips required for MEMORY PLUS are INTEL 2716 or equivalent (Texas Instrument 2516 but NOT T. I. 2716). This chip has the following basic parameters:

SPEED: 450 nanosecond access time

POWER: 105 milliamp worst case current, and

single +5 volt required

The MEMORY PLUS EPROM is organized into a single contiguous 8K block of memory. The location of the EPROM in the MICRO addressing space is defined by a switch which may be set to start at any 8K boundary (2K hex boundary). See the chart of switch positions on the preceding page. The position is determined by the flat section of the switch.

(KIM 1 ONLY): If, and only if, the "EK" address is used, then the jumper "J1" (located on the top side of component U4) must be changed. The existing jumper etched on the board must be cut and a wire run from the hole nearest the "J" to the hole nearest the "1". This will cause interrupts to be serviced by the FFFx vectors instead of the lFFx KIM-1 vectors.

The EPROM sockets are addressed such that the socket nearest the edge of the board has the lowest address. The exact layout of the individual EPROM chips may be found in a diagram in the section on "MEMORY PLUS Testing and Field Repair".

VIA Address Selection

There are several ways to address the MEMORY PLUS VIA chip. There is circuitry on the board which will normally address the VIA starting at 6200. This is accomplished by combining the 6000 signal generated by the 74LS138 at U4, pin 12, with address lines A8 and A9 in the 74LS32 at U6. If this address is in conflict with something in your system, it may be changed in several ways. The easiest change is to use any other available (unused) decode signal from the 74LS138 at U4. Simply unsolder the existing wire from pin 12 and attach it to the new pin. In this way you can have the VIA addressed as 2200, 4200, 6200 (which is the way the MEMORY PLUS board is shipped), 8200, A200, or C200. If these other addresses do not solve your problem, then you can provide from an external source a signal at pin L of the Application Connector in place of the signal from U4 discussed above. The U4 wire must be disconnected. The VIA address will be the value of the external signal to pin L, plus 0200. example, using the K5 signal (1400) from the KIM-1 or SYM-1 will cause the VIA addresses to start at 1600 (1400 + 0200 = 1600). IMPORTANT NOTE: If you do change the VIA address, then locations 0006 and 0007 in the EPROM Programming Program must be changed before using it.

VERSATILE INTERFACE ADAPTER

The 6522 Versatile Interface Adapter is one of the important pluses of MEMORY PLUS. This sophisticated chip has the following basic features:

I/O: Two 8-bit parallel I/O ports with additional handshaking control lines. This more than doubles the basic KIM-1 I/O capabilities.

TIMERS: Two powerful interval timers which have a number of operating modes permitting them to be used as counters, "free-running" timers, "one-shot" timers, and more.

SHIFT REGISTER: Perform serial I/O under control of a timer, the system clock or an external signal. Serial-to-parallel and parallel-to-serial conversions take place within the 6522 without involving the MICRO on a bit-by-bit basis.

INTERRUPTS: The many different devices on the 6522 can cause interrupts to signal the completion of activity. These interrupts can be individually enabled, disabled and tested.

The 6255 chip has two functions on MEMORY PLUS. The first is to provide all of the 6522 capabilities to the user as an extension of the MICRO. The second is to control the EPROM Programmer. The 6522 is the heart of the EPROM Programmer. When the system is being used to program EPROMs, then the 6522, as well as several I/O lines from the basic MICRO, is dedicated to this task. See the section on "EPROM Programming" for details.

The addressing of the 6522 is determined by a +5 signal generated by the MEMORY PLUS board and the AB8 and AB9 address signals. The sixteen internal registers of the 6522 normally have the following addresses and functions:

6200	ORB Outp	ut Register B/Input Register B
6201	ORA Outp	ut Register A/Input Register A With Handshake
6202	DDRB Data	Direction Register B
6203	DDRA Data	Direction Register A
6204	T1C-L	Timer/Counter 1 Low
6205	T1C-H	Timer/Counter 1 High
6206	T1L-L	Timer/Counter 1 Low
6207	T1L-H	Timer/Counter 1 High
6208	T2C-L	Timer/Counter 2 Low
6209	T2C-H	Timer/Counter 2 High
620A	SR	Shift Register
620B	ACR	Auxiliary Control Register
620C	PCR	Peripheral Control Register
620D	IFR	Interrupt Flag Register
620E	IER	Interrupt Enable Register
620F	ORA2	Output Register A/Input Register A Without Handshake

EPROM Programming

The usefulness of the EPROMs on the MEMORY PLUS board is enhanced by the inclusion of on board EPROM programming facilities. The INTEL 2716 EPROM is electrically programmable and ultraviolet light erasable. The user can buy or build an ultraviolet light eraser. MEMORY PLUS provides the parts required for the programming of the EPROMs. These parts consist of the following items:

- EPROM Programming Socket: Socket 79 is a 24 pin socket located toward the lower right hand corner of the board. The EPROM to be programmed is placed in this socket.
- +25 Volt Regulator: +25 volts is required for programming the 2716.

 This may be provided directly by the user at pin A-22 of the MEMORY PLUS application connector. Since this voltage is so critical, and since an over voltage can destroy an EPROM, an on board regulator circuit is provided. This will provide about 24.7 volts when supplied with +27 to +30 volts at pin E-3 of the MEMORY PLUS expansion connector. **SEE NOTE OF PAGE 18.
- Control Lines: The EPROM requires eleven (11) address lines, eight (8) data lines, and two (2) control lines. All but three of these lines are provided by the MEMORY PLUS VIA 6522. The remaining three lines come from the MICRO port B: PBO, PB1, and PB2.
- Timing: EPROM programming requires a 50 millisecond pulse be applied to the EPROM. The VIA 6522 includes a timer which is used for timing this interval.
- EPROM Programming Program: The control of the programming is handled by a program run on the MICRO. This program is provided in the form of a source listing in this manual and as a cassette tape included in the MEMORY PLUS package.

The 2716 EPROM may be programmed one location (byte) at a time, or the entire EPROM may be programmed. The steps required to program the EPROM are:

- 1. With the power off, insert the EPROM to be programmed into the Programming Socket.
- 2. Turn on the power and load the data to be copied into the EPROM into any portion of memory. This may be RAM memory loaded from cassette (or by hand) or may be another EPROM which is going to be copied.
- 3. Load the EPROM Programming Program from cassette (or by hand) into memory (locations 0000 to 00D8)
- 4. Make sure the following application connector connections are in place: MICRO A-9 TO MP A-19; MICRO A-10 TO MP A-20; MICRO A-11 TO MP A-21

5. Set up the following parameters for the EPROM Programming Program:

0000 and 0001 Starting address of memory to be copied from.
0002 and 0003 First address in EPROM to be copied to.
0004 and 0005 Last address +1 of memory to be copied from.

For example, to copy from RAM locations 2000 through 217A into the EPROM starting at location 0300, the following values would be set:

0000 00 Low byte of Starting address 2000
0001 20 High byte of Starting address 2000
0002 00 Low byte of First address in EPROM 0300
0003 03 High byte of First address in EPROM 0300
0004 7B Low byte of Last address +1 217A = 7B
0005 21 High byte of Last address +1 217A

- 6. Turn on +25 volt supply connected to MP A-22 or unregulated +27 to +30 volt supply connected to MP E-3. See Note of Phone 18.
- 7. After double checking that all prior steps have been done correctly, start the program at 0011.
- 8. It will take about 50 milliseconds per location for programming. This means about 100 seconds to program an entire 2K EPROM. When the program is done it will return to the MICRO Monitor with an address which will indicate successful completion of the requested programming. The address value is given in the table in 10. below.
- 9. Turn off the +25 volt (or +27 to +30 volt) supply and the rest of the power to the system. Then remove the EPROM from the programming socket. The EPROM may now be placed in its operational socket and used.
- 10. The EPROM Programming Program performs several tests and may exit to the Monitor to indicate an error or successful completion. The address which will be displayed depends on which Monitor/MICRO you are using.

AIM 00B8 Program ran successfully to completion.

SYM OOBA

AIM 009E A Verify error. The correct data has not been programmed KIM 009F into the EPROM. This may be caused by: SYM 00A0

An EPROM which was not "clean" (all 1's) to start.

A defective EPROM.

One or more address lines from the MICRO not properly hooked up or not properly functioning.

AIM 00A9 A Starting address error. The memory address pointer has KIM 00AA tried to go beyond location FFFF. This may be caused by: SYM 00AB

Providing an incorrect Starting address in locations 0000 and 0001.

Providing an incorrect Last address in locations 0004 and 0005.

AIM 00C3 An EPROM address error. The EPROM address pointer has tried to go beyond location FFFF. This may be caused by:

SYM 00C5

Providing an incorrect First address in locations 0002 and 0003.

Providing an incorrect Last address in locations 0004 and 0005.

The following connections must be made between the MICRO and the MEMORY PLUS board before any EPROM Programming can take place:

MTCRO	A-9 to MP A-19	Port	В	Bit	0	(PBO)	Address	Bit	8	for	EPROM .
	A-10 to MP A-20	The Village Control of the					Address				
	A-11 to MP A-21	Port	B	Bit	2	(PB2)	Address	Bit	10	for	EPROM

If the MEMORY PLUS board is mounted in its normal position, directly below the MICRO, it may be difficult or impossible to get access to the EPROM socket for programming. There are two ways around this problem.

- 1. Use a 24 pin header to bring wires directly from the EPROM Programming Socket out to a more accessible location.
- 2. Attach wires for an additional EPROM Programming Socket directly to the MP application connector. All of the lines necessary for attaching an external EPROM Programming Socket are available:

EPROM		plication nnector	Function
1		A-15	Address bit 7 from VIA PB7
2		A-B	Address bit 6 from VIA PB6
3		A-16	Address bit 5 from VIA PB5
3		A-13	Address bit 4 from VIA PB4
			Address bit 3 from VIA PB3
5		A-12	Address bit 2 from VIA PB2
6		A-11	Address bit 1 from VIA PB1
7		A-10	Address bit 0 from VIA PB0
8		A-9	
9		A-14	Data bit 0 from VIA PAO
10		A-2	Data bit 1 from VIA PA1
11		A-3	Data bit 2 from VIA PA2
12		A-1	Ground
13		A-4	Data bit 3 from VIA PA3
14	100 March 201	A-5	Data bit 4 from VIA PA4
15		A-6	Data bit 5 from VIA PA5
. 16		A-7	Data bit 6 from VIA PA6
17		A-8	Data bit 7 from VIA PA7
18		A-18	Program Pulse Inverted from VIA CB2
19	(MICRO A-11)	A-21	Address bit 10 from MICRO PB2
20		A-F	Chip Select from VIA CA2
21		A-22	+25V direct or from +27 to +30 regulator
22	(MICRO A-10)	A-20	Address bit 9 from MICRO PB1
23	(MICRO A-9)		Address bit 8 from MICRO PBO
24	(MICRO A-A)	A-A	+5V regulated

The addressing for the EPROM Socket only consists of eleven (11) bits. This means that addressing for programming purposes runs from 0000 to 07FF, regardless of the actual address that the EPROM will eventually reside at. The high order five (5) bits of EPROM address are totally defined by which socket the EPROM is placed in and where the set of EPROMs are switched to: 2000, 4000,..., E000.

PROM ORG \$0000

ACCESS * \$8B86 SYM-1 ACCESS ENTRY

VIA REGISTER OFFSETS

	ORB ORA DDRB DDRA TTWOL TTWOH PCR IFR IER	* * * * * * * * * * * * * * * * * * *	\$0001 \$0002 \$0003 \$0008 \$0009 \$0000	OUTPUT REGISTER B OUTPUT REGISTER A DATA DIRECTION REGISTER B DATA DIRECTION REGISTER A TIMER TWO LOW TIMER TWO HIGH PERIPHERAL CONTROL REGISTER INTERRUPT FLAG REGISTER INTERRUPT ENABLE REGISTER	
G000 C0 0001 00 0002 00 0003 C0 0004 00 0005 00 0006 00 0007 62 0008 4C 00C9 00 000A C0 000B C0 000C OC 00CD OC 00CD OC	SAL SAH PRMLOW PRMHGH EAL EAH VIA JMPMON MONTOR INTVEC PBDD PBD		\$00 \$00 \$00 \$00 \$00 \$00 \$00 \$62 \$4C \$00 \$00 \$00 \$00 \$00 \$00	STARTING ADDRESS LOW STARTING ADDRESS HIGH EPROM LOW ADDRESS EPROM HIGH ADDRESS END ADDRESS LOW END ADDRESS HIGH POINTER TO VIA NORMALLY AT 6200 JUMP TO MONITOR POINTER TO SYSTEM MONITOR FOR RETURN FROM PROGRAMMER POINTER TO INTERRUPT VECTOR PORT B DATA PORT B DATA	
0011 A9 00 0013 48 0014 28 0015 A2 E0 0017 AD FD FF 001A C9 8B 001C F0 0A 001E A2 D0 0020 C9 E0 0022 F0 07 0024 A2 D8 0026 D0 03 0028 20 86 8B	KIM	LDA CMPIM BEQ LDXIM CMPIM BEQ LDXIM BNE	STABLE \$FFFD \$8B SYM ATABLE \$EO MOVE KTABLE MOVE		
002B 86 30 002D A2 07 002F B5 00 0031 95 09 0033 CA 0034 10 F9	MOVE	STXZ LDXIM LDAX STAX DEX	\$07 \$00 MONTOR	+O1 SETUP POINTER	

0036 0038 0039	48	00	ENTER	LDAIM PHA PLP	\$00	CLEAR ALL STATUS FLAGS
003A 003C 003E 0040 0042	AO A9 91 A9	C5 OB		LDYIM LDAIM STAIY		GET INTERRUPT POINTER SETUP IN TABLE
0042 0043 0045 0047 0049	91 A9 A0	EC OC		STAIY LDAIM LDYIM	PCR	SETUP VIA VALUES
CO4B 004D CO4F	AO A9 91	0E 7F 06		LDAIM STAIY	IER \$7F VIA	DISABLE ALL INTERRUPTS
0051 0053 0055 0057	A 9 91 A D	FF C6 OE		LDYIM LDAIM STAIY LDYIM	\$FF VIA IER	CLEAR INTERRUPT PENDING
0059 005B				LDAIM		ENABLE TIMER TWO
005D 005F 0061 0063 0065 0067	A9 A0 91 AC 91	FF 02 06 03 06	NEXT	LDAIM LDYIM STAIY LDYIM STAIY	DDRB VIA DDRA VIA	INIT X RECISTER SET DATA DIRECTION
0069 006B 006D 006F 0071 0073 0075	A5 81 A5 81 A1 A0	06 03 0F 00 01		LDYIM	PRMLOW VIA PRMHGH PBD SAL CRA	CUTPUT NEXT ADDRESS LOW 8 BITS BITS 8, 9, 10 GET DATA BYTE CUTPUT VIA CRA
0077		50	TIMER		VIA \$50	SETUP 50 MILLISECOND TIMER
007B 007D 007F 0081	A D 91 A 9 A D	08 06 03 09	TITLE	LDYIM STAIY LDAIM LDYIM	TIWOL VIA \$C3 TIWOH	OUTPUT TO TIMER TWO LOW HIGH BYTE OF TIMER
0083 0085 0087 0089	A9 AD	CE OC				OUTPUT TO TIMER TWO HIGH PROGRAM HIGH, PROGRAM MODE
008B			TIAW	CPYIM BEQ	PCR WAIT	TEST FOR INTERRUPT SERVICED ELSE, WAIT FOR IT
008F 0091 0093 0095	A0 91 A0	03 06 01	VERIFY	LDYIM STAIY	DDRA	VERIFY PROGRAMMING SET ORA FOR INPUT SETUP POINTER
0097	Bl	06		LDAIY	VIA	

0099 C1 00 0098 F0 03 009D 20 08 00		BEQ	DKAY	COMPARE ORIGINAL DATA GOOD IF MATCH EXIT ON ERROR
ODAO E6 OO OOA2 DO O7 OOA4 E6 O1 OOA6 DO O3 COA8 20 O8 OO	OKAY	BNE INC	SAH TEST	BUMP DATA POINTER BRANCH IF NOT ZERO BUMP HIGH DATA POINTER BRANCH IF NOT ZERO EXIT ON ERROR
00AB A5 05 00AF C5 01 00AF D0 09 00B1 A5 04 00B3 C5 00 00B5 D0 03 00B7 20 08 00	TEST	LDA CMP BNE LDA CMP BNE JSR	SAH MORE EAL SAL MORE	TEST ALL DONE BY COMPARING POINTERS
00BA E 6 02 00BC DO 9F 00BE E 6 03 00CO DO 9B 00C2 20 08 00	MORE	INC BNE INC BNE JSR	NE XT PRMHGH NE XT	BUMP PROM POINTERS READY IF NOT ZERO BUMP HIGH POINTER OKAY IF NOT ZERO EXIT ON ERROR
COC5 A9 EC OOC7 91 O6 COC9 AO OD OOCB B1 O6 OOCD 91 O6 OOCF 40	INTRPT	STAIY LDYIM LDAIY	\$EC VIA IFR VIA VIA	SETUP TO CLEAR INTERRUPT READ AND WRITE TO CLEAR
00D0 6D 00D1 E1 00D2 0C 00D3 A4 00D4 02 00D5 A0 00D6 00 00D7 AC	ATABLE	= = = = = = = = = = = = = = = = = = = =	\$6D \$E1 \$00 \$A4 \$02 \$A0 \$A0 \$A0	TO DISPLAY PC COUNTER
00D8 05 00D9 1C 00DA FE 00DB 17 00DC 03 00DD 17 00DE 02 00DF 17	KTABLE		\$05 \$1C \$FE \$17 \$03 \$17 \$02 \$17	KIM MONITOR ENTRY IRQ INTERRUPT POINTER PBDD PBD
00E0 35 00E1 80 00E2 7E 00E3 A6 00E4 02 00E5 A0 00E6 00	STABLE	=======================================	\$35 \$80 \$7E \$A6 \$02 \$A0	SYM ENTRY POINT IRQ INTERRUPT POINTER PBDD PBD
COE7 AO		Ξ	\$A0	16

MEMORY PLUS Testing and Field Repair

Your MEMORY PLUS board has been burned in and tested before shipment. If, after following the steps outlined in the "Setting Up MEMORY PLUS" section, the board does not seem to work properly, or if it ever seems to stop functioning correctly, then the following steps should be taken.

1. Check that the board is receiving adequate power.

Place the ground lead of a voltmeter or 'scope on any convenient ground on the board (the left lead of the large capacitor at the upper left hand corner of the board is handy) or on the connector (A-1, E-1, E-22, E-A, or E-Z).

Measure the +5 volts at each of the four jumpers on the Header located near the voltage regulators. If you are providing unregulated +8 to +10 volts, then the top jumper should have this value. If you are using regulated +5 volts, then the top jumper should show +5V. The bottom three jumpers should show +5V in any case. If not, check your supply. If one of the three shows a voltage other than +5, it indicates a problem with the associated voltage regulator which might require replacement. The bottom jumper comes from Q6, the next jumper from Q5, and the next to top jumper from Q4. (See diagram on page 25).

Measure the +25 volts at pin A-22 of the MEMORY PLUS application connector. If you are providing unregulated +27 to +30 volts, the output of the +25 volt regulator circuit should show about +24.7V. If you are providing regulated +25 volts at this pin, it will show the output of your power supply. If the value for the unregulated situation is not +24.7, then check your unregulated voltage at pin E-2 of the MEMORY PLUS expansion connector. It must be +27 to +30V.

- 2. Check that all IC chips are firmly in their sockets. It is possible for chips to come loose during handling and shipping. Push each chip firmly into its socket.
- 3. Check that the Header is in the proper position for the method of providing +5 volts. If you are providing +5 at pins E-21 and E-Y, then the Header should have its notched corner at pin 9 and the jumper wires should go from pins 2-15, 4-13, 6-11, and 8-9. If you are providing unregulated +8 to +10 volts at pins E-19 and E-20, then the Header should have its notched corner at pin 1 and the jumper wires should go from pins 1-16, 3-14, 5-12, and 7-10.
 - 4. Check all of the connections between the MICRO, MEMORY PLUS, and the power supplies.
 - 5. Follow the instructions in the "RAM Memory Test" section if the RAM Memory appears to be having problems.
 - 6. Check the MICRO or try MEMORY PLUS with a different MICRO. For EPROM Programming it is absolutely essential that bits 0, 1, and 2 of the MICRO Port B are functioning properly (PBO, PBI, and PB2). A quick test of Port B may be made by putting FF in location PBDD and then trying to write 07 in location PBD. If this does not work, then you have a problem and should not attempt to program any EPROMs until you have the MICRO serviced.

Remember that you are exercising your MICRO in ways you may have never tried before. This will, in some cases, uncover faults that have existed undetected in a MICRO. For example, my own "reliable" Kim-1 which I had been using extensively for well over a year, turned out to have a defective Port B. Bits O and 1 which I had been using for cassette control worked fine, but bit 2 did not. I zapped a few EPROMs, not fatally thank goodness, before discovering this. Another KIM-1 I used had flakey memory in Page Zero such that the RAM Memory Test would not work. So, it really can happen.

7. Check all MEMORY PLUS switches and jumpers. In addition to the Header which was discussed in 1. and 3. above, there are two switches and a jumper to be concerned with:

The RAM Address Select Switch (see page 8) must be set to "2K" for the Memory Test to work as documented. Actually, the memory test will work with any addresses, as long as the correct parameters are set in page zero location 0000 - start page number = first page to test and location 0001 - end page number = last page to test. The RAM switch must be selecting the bank of memory you are attempting to test, and it may not be selecting the same chunk of memory as the ROM select switch.

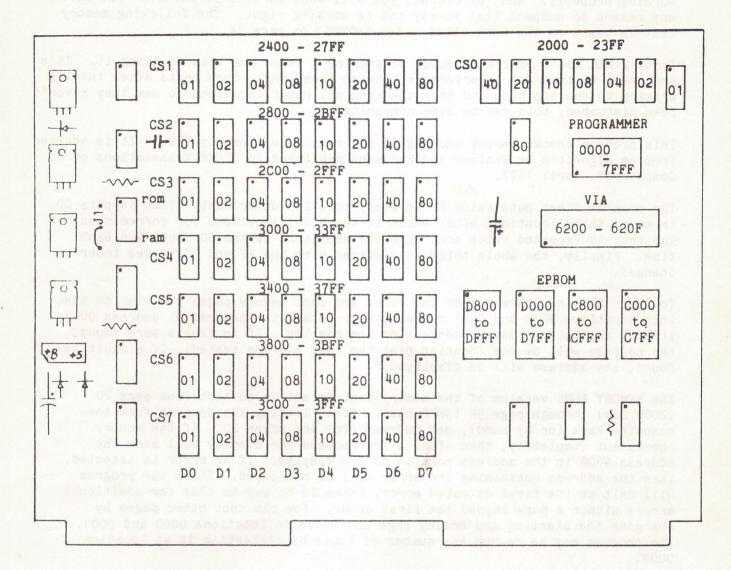
The ROM Address Select Switch (see page 8) must not be set to the same starting address as the RAM switch. If the ROM switch is set to "EK", then there will be conflict with the MICRO Monitor interrupt vectors unless the jumper changes discussed on page 9 have been made, since the board comes with the jumper set so that interrupts will be decoded by the MICRO Monitor locations 1FFA through 1FFF. If you put ROM in E000 to FFFF, then this jumper must be changed. Otherwise any address in this range will be decoded twice: as E000 to FFFF and 0000 to 1FFF.

8. Check that all EPROMs are inserted in the proper direction. Pin 1 in the EPROM Programming Socket is in the upper left corner. Pin 1 in the EPROM normal sockets is in the upper right corner.

MEMORY PLUS was designed for easy field repair. It is, of course, hoped that no repair will ever be required on your unit. If some repair is required, then it is hoped that it can be done by the user or some local source. The unit should only have to be sent back for factory servicing in rare circumstances. This means that your MEMORY PLUS board should never be down very long.

WARNING:

Do NOT connect +5V Battery to E-2
or +27 Unreg. to E-3 if these lines
are connected to your microcomputer
via a cable of MOTHER board as these
voltages could damage your computer.
If these two voltages are to be used
(for battery backup and EPROM programming)
make sure they are isolated from the
rest of your system.



The dot in one corner of each IC chip and Header indicates the proper location of pin 1. The Header has two corners marked, one labelled +5 and one labelled +8. These indicate the proper orientation of the Header when the power supply is providing a regulated +5 volts or an unregulated +8 to +10 volts.

ROM and RAM show the location of the switches used to select the base address for the ROM and RAM memories.

J1 marks the location of the jumper which must be changed if ROM is placed to start at E000. The line shown is the etched jumper which causes interrupt addresses (FFFA to FFFF) to select the KIM-1 Monitor interrupt vectors (1FFA to 1FFF). This jumper must be removed and replaced by a jumper from the dot near the J to the dot near the 1 if interrupts are to be decoded by the high addresses.

RAM Memory Test

You should test the MEMORY PLUS RAM when you initially set up your system. You may also want to test it from time-to-time to make sure it is all still working properly. And, of course, you will want to test it whenever you have any reason to suspect that it may not be working right. The following memory test is based on the work cited under "NOTES" on page 24.

"Testing RAM isn't just a question of storing a value and then checking it. It's important to test for interference between locations. Such tests often involve writing to one location and then checking all other locations to see they haven't been disturbed; this can be time consuming.

This program checks memory thoroughly and runs exceptionally fast. It is adapted from an algorithm by Knaizuk and Hartmann published in "IEEE Transactions on Computers", April 1977.

The program first puts value FF in every location under test. Then it puts 00 in every third location, after which it tests all locations for correctness. The test is repeated twice more with the positions of the 00's changed each time. Finally, the whole thing is repeated with the FF and 00 values interchanged.

To Run: Set the addresses of the first and last memory pages you wish to test into locations 0000 and 0001 respectively. Start the program at address 0002; it will halt with a memory address on the display. If no faults were found, the address will be one location past the last address tested. If a fault is found, its address will be displayed."

The MEMORY PLUS version of the memory test is set up to test from page 20 (2000 hex) through page 3F (3FFF hex). After loading the program from the cassette tape (or by hand), set address 0002 and press GO. If the memory checks out completely, then after a few seconds the display will show the address 4000 in the address portion of the display. If an error is detected, then the address containing the error will be displayed. Since the program will halt at the first detected error, there is no way to test for additional errors within a page beyond the first error. You can test other pages by changing the starting and ending page addresses in locations 0000 and 0001. The program may be re-run any number of times by restarting it at location 0002.

Once a bad location has been detected, you can examine the location via the MICRO Monitor and perhaps determine the problem. For example, if the location has a data value of 7F, it would indicate that the most significant bit was not working. Refering to the Memory Organization drawing you could determine which 2102 chip was responsible for this bit. Since the RAM chips are all socketted, it is a simple matter to remove the suspect chip and replace it with another chip. Even if you do not have any spare 2102 chips handy, you can swap the suspect chip with another chip and see if the problem moves with the chip or stays in the same location. IMPORTANT NOTE: Turn the power off when removing any chips, otherwise you may destroy the memory chips. If the problem moves with the chip, then the solution is to get a replacement chip. If the problem does not move with the chip, then you must look elsewhere for the solution.

The next test would be to swap the 74LS367 chips and see if the problem shifted. Then the 74LS138 chips could be swapped. Finally you could replace the 74LS00, 74LS32, or 74LS04 chips. Note that the replacements do not have to be "LS" type. One of the above chip replacements should solve 99% of the problems which occur in the field.

```
MEMORY TEST 9 FEBRUARY 1979
             MEMORY ORG $0000
                       $8B86 SYM-1 ACCESS ENTRY
              ACCESS *
              OUTBYT * $82FA SYM-1 OUTPUT BYTE
SCANDS * $8906 SYM-1 SCAN DISPLAY
                         $1C4F KIM-1 ENTRY POINT
$00FA KIM DISPLAY POINTERS
              GOKIM *
              LPOINT *
              HPOINT * $00FB
                         $EF7B AIM 65 OUTPUT ASCII
             ASCOUT *
         BEGIN =
                               STARTING TEST PAGE
0000 20
                      $20
$3F
0001 3F
             END =
                               ENDING TEST PAGE
0002 A9 00 START LDAIM $00 ZERO POINTERS
0004 A8 TAY FOR LOW ORDER ADDRESSES
0005 48 PHA SET ALL STATUS BITS TO ZERO
0006 28 PLP
0007 85 D1
                  STAZ POINTL
             BIGLP STAZ FLAG = 00 FIRST PASS, = FF SECOND PASS
0009 85 D3
000B A2 02
                   LDXIM $02
                   STXZ PASS SET 3 TESTS EACH PASS
000D 86 D5
         NPASS LDAZ BEGIN SET POINTER TO
STAZ POINTH START OF TEST AREA
LDXZ END
000F A5 00
0011 85 D2
0013 A6 01
                   LDAZ FLAG
0015 A5 D3
0017 49 FF
                   EORIM $FF REVERSE FLAG
STAZ FLIP = FF FIRST PASS, = 00 SECOND PASS
0019 85 D4
001B 91 D1 CLEAR STAIY POINTL WRITE FLIP VALUE
001D C8 INY TAIL CONTROL
                   INY
                              INTO ALL LOCATIONS
              BNE CLEAR
OO1E DO FB
                INCZ POINTH
0020 E6 D2
0022 E4 D2
                 CPXZ POINTH
0024 BC F5
                  BCS CLEAR
            FLIP VALUE IN ALL LOCATIONS. NOW CHANGE 1 IN 3
0026 A6 D5 LDXZ PASS
CO28 A5 CO LDAZ BEGIN SET POINTER
CO2A 85 D2 STAZ POINTH BACK TO START
002C A5 D3
                   LDAZ FLAG CHANGE VALUE
          FILL
CO2E CA
          TOP
                   DEX
                   BPL SKIP SKIP 2 OUT OF 3
002F 10 04
          BPL SKIP SKIP 2 OUT OF 3
LDXIM $02 RESTORE 3 COUNTER
STAIY POINTL CHANGE 1 OUT OF 3
0031 A2 02
                   STAIY POINTL CHANGE 1 OUT OF 3
0033 91 D1
          SKIP
0035 CE
                   INY
0036 DO F6
                        TOP
          INCZ POINTH NEW PAGE
0038 E6 D2
```

003A 003C 003E	C5	D2			CMPZ	POINTH	HAVE WE PASSED END OF TEST AREA? NO. KEEP GOING
				MEMORY	SET UF	. NOW	TEST IT
0040 0042 0044	85	D2			STAZ	POINTH	SET POINTER BACK TO START SET UP 3 COUNTER
0046 0048 0049 004B 004D	CA 10 A2	04			DE X BPL LDXIM	SLIP \$02	TEST FOR FLIP VALUE 2 OUT OF 3 TIMES OR 1 OUT OF 3 TIMES TEST FOR FLAG VALUE
004F 0051 0053 0054 0056 0058 005A 005C	DO C8 DO E6 A5 C5	15 F 0 D 2 01 D 2			BNE INY BNE INCZ LDAZ	OUT POP POINTH	TEST END
				ABOVE	TEST OF	KAY. CH	HANGE AND REPEAT
005E 0060 0062 0064 0066	10 A5 49	AD D3 FF			BPL LDAZ	NPASS FLAG \$FF	CHANGE 1 IN 3 POSITION AND DO NEXT PASS INVERT FLAG FOR PASS TWO AND REPEAT BIG LOOP
0068 006A 006D 006F 0071 0073	AD C9 FO C9	FD 8B 46 E0	FF		LDA CMPIM BEQ	POINTL \$FFFD \$8B SYM \$EO AIM	PUT LOW ORDER ADDRESS FOR DISPLAY TEST HIGH BYTE OF INTERRUPT VECTOR = SYM-1 = AIM 65
0075 0077 0079 007B 007D	85 A5 85	FA D2 FB	1C	KIM	LDAZ STAZ LDAZ STAZ JMP	LPOINT POINTH HPOINT	MOVE POINTERS FOR KIM RETURN TO KIM MONITOR
0080 0082 0084 0086 0088 008A 008C	85 85 85 A2 A1 85	D6 D1 D7 00 D1 D8	ë	AIM	STAZ LDAZ STAZ LDXIM LDAIX STAZ	AHIGH POINTL ALOW \$00 POINTL ADATA	MOVE DATA FOR AIM DISPLAY GET DATA AT ADDRESS START AT POSITION 19.
0090	8A			ALOOP	TXA		SAVE X VALUE

```
0091 48
                      PHA
                                   ON STACK
CC92 AC C4
                                   SHIFT 4 POSITIONS PER CHARACTER
                      LDYIM $04
0094 A5 D8
                      LDAZ ADATA
                                   GET DATA
0096 29 OF
                      ANDIM $OF
                                   MASK TO NIBBLE
CO98 C9 CA
                      CMPIM $0A
                                   TEST DECIMAL
009A 30 03
                      BMI
                            AOKAY
                                   DECIMAL
                      CLC
CO9C 18
                                   A - F. MUST CONVERT TO
009D 69 07
                      ADCIM $07
                                   ASCII
009F 18
               ADKAY
                      CLC
                                   FINISH CONVERSION
00AC 69 BC
                      ADCIM $BO
                                   ASCII + AIM FLAG
00A2 20 7B EF
                      JSR
                            ASCCUT CUTPUT TO DISPLAY
00A5 46 D6
               AMOVE
                      LSRZ
                            AHIGH MOVE TO NEXT NIBBLE
00A7 66 D7
                      RORZ
                            ALOW
00A9 66 D8
                      ROR7
                            ADATA
00AB 88
                      DEY
ODAC DO F7
                      BNE
                            AMOVE
                                   RESTORE X
00AE 68
                      PLA
ODAF AA
                      TAX
OOBO CA
                      DEX
                                   DONE?
COB1 EO CE
                      CPXIM $0E
COB3 BC DB
                      BCS
                            ALCCP
                                   NO
OCB5 90 C9
                      BCC
                            AIM
                                   YES. REPEAT
COB7 20 86 8B SYM
                      JSR
                            ACCESS ENABLE SYM MOEMORY
OOBA A5 D2
                      LDAZ
                           PCINTH
                            OUTBYT OUTPUT
OOBC 20 FA 82
                      JSR
OOBF A5 D1
                      LDAZ
                            POINTL
OOC1 20 FA 82
                      JSR
                            OUTBYT
00C4 AC CC
                      LDYIM $00
00C6 B1 D1
                      LDAIY POINTL GET DATA
OCC8 20 FA 82
                      JSR
                            CUTBYT
COCB 20 06 89 DISPLY JSR
                            SCANDS SCAN DISPLAY
OOCE 4C CB OO
                      JMP
                            DISPLY CONTINUE
00D1 00
              POINTL =
                            $00
00D2 00
              POINTH =
                            $00
00D3 00
              FLAG
                    =
                            $00
COD4 CC
              FLIP
                     =
                            $00
00D5 00
              PASS
                     =
                            $00
00D6 00
                    =
              AHIGH
                            $00
COD7 00
              ALOW
                     =
                            $00
0008 00
              ADATA
                            $00
```

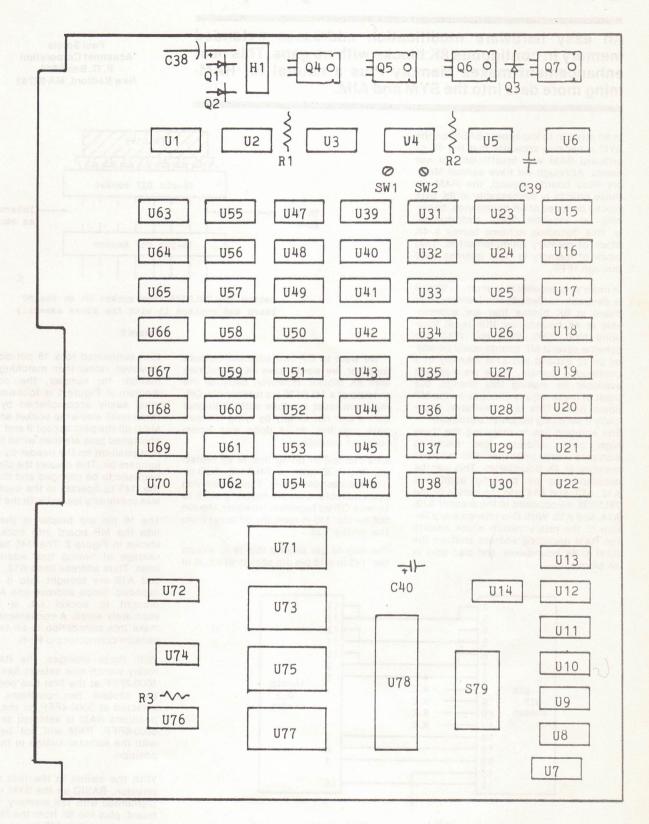
MEMORY PLUS Parts List

ITEM	PART	Qty.	DESCRIPTION
1.	U1, U2, U72	3	IC 74LS367 Hex Bus Driver with 3-state outputs
2.	U3, U4, U76	3	IC 74LS138 3-to-8 Line Decoder
3.	U5	1	IC 74LS00 Quad 2-Input Positive NAND Gates
4.	U6	1	IC 74LS32 Quad 2-Input Positive OR Gates
5.	U74	1	IC 74LS04 Hex Inverter
6.	U7 - U70	64	Memory Element 2102 450 nanosec, low power
7.	SW1, SW2	2	1-of-7 Rotary Switch
8.	R1 - R3	3	Resistor 3.3K, 1/4 watt
9.	C1 - C37	37	Capacitor .01 MFD, 50WV DC
10.	C38	1	Electrolytic Capacitor 22 - 25 MFD, 25V
11.	C39	1	Capacitor .001 MFD
12.	C40	1	Electrolytic Capacitor 3 - 5 MFD, 35V
13.	Q1, Q2, Q3	3	Diodes 1N4001 Rectifier 50V
14.	Q4, Q5, Q6	3	Voltage Regulator LM340T-5, +5V, 1.0A
15.	Q7	1	Voltage Regulator LM340T-24, +24V, 1.0A
16.	HS1 - HS3	3	T220 Heat Sink (Large)
17.	HS4	1	T220 Heat Sink (Small) (may be omitted)
18.	S1 - S4, S7 - S70, S72, S76, S80	71	IC Socket 16 pin
19.	S5, S6, S74	3	IC Socket 14 pin
20.	S71, S73, S75, S77,	5	IC Socket 24 pin
	S79		
21.	S78	1	IC Socket 40 pin
22.	H1	1	IC Socket Header 16 pin
23.	U78	1	VIA 6522 Versatile Interface Adapter
	Accessories Package		

3 Battery Clip 9V transistor battery type

NOTES:

- 1. The Memory Test is adapted from "Memory Test" by Jim Butterfield which appears on pages 122 and 123 of THE FIRST BOOK OF KIM, edited by Butterfield, Ockers and Rehnke, published by Hayden Book Company. The book sells for \$9.00 and is a must for any 6502 user.
- 2. The program listings in this manual were produced by the Micro-ADE Assembler on a KIM-1 with a MEMORY PLUS board. The COMPUTERIST version of Micro-ADE includes a cassette tape with two versions of Micro-ADE. One has the program in 2000 to 2FFF and uses 3000 to 3FFF for the Source and Symbol working areas. The other has the program in C000 to CFFF and uses 2000 to 3FFF for the Source and Symbol working areas. This second version is ready to be placed into EPROM and left resident in your MEMORY PLUS board. Micro-ADE costs \$25.00 for the Operators Manual and Cassette Tape. This Manual includes most of the Input/Output Source Listings so that the user can customize the package to his type of terminal. Complete Source Listings are available for an additional \$25.00.



SYM and AIM Memory Expansion

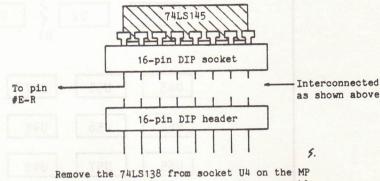
An easy hardware modification addresses extended memory in contiguous 8K blocks with no gaps. This neat enhancement makes Memory Plus a natural for RAMming more data into the SYM and AIM.

Paul Smola Acushnet Corporation P. O. Box E916 New Bedford, MA 02742

In an attempt to implement BASIC on the SYM it became apparent that the 4K of onboard RAM was insufficient for our needs. Although we have several Memory Plus boards around, the RAM on these boards is addressable in 8K byte blocks decoded at 8K boundaries, beginning at location 2000. Unfortunately, this decoding scheme leaves a 4K block of memory unimplemented. That block of memory is from address 1000 through 1FFF.

In order to overcome this shortcoming, it is desirable to decode the Memory Plus board in 8K blocks that are addressable at 4K boundaries; that is, at locations 1000, 3000, 5000, etc. With this scheme several MP boards could be added on to expand the SYM memory in a continuous fashion. There are methods available for making this change, but most of these require changes on the MP board itself. This is undesirable, especially if servicing becomes a problem.

The solution lies in replacing the three high order address line decoding schemes with one that will address memory at 4K boundaries. This can be accomplished by bringing addresses A12, A13, and A14 into the inputs of the 74LS138, as opposed to the present A13, A14, and A15. With this change any position of the rotary switch which selects the RAM decoding address enables the RAM at 4K boundaries, and also only in 4K blocks.



Remove the 74LS138 from socket U4 on the MP board and replace it with the above assembly

Figure 2

If we were to OR two adjacent outputs together, we would have 4K boundaries with 8K blocks. However, because the outputs of a 74LS138 are totem-pole, ORing them must be done with additional gating and not simply by tying the outputs together, as is done with open-collector outputs.

One method of doing this is by replacing the '138 with a 74LS145 BCD-to-decimal decoder driver. This device has open collector outputs enabling them to be wire OR'ed together. However, the pin out on the '145 is radically different from that on the '138.

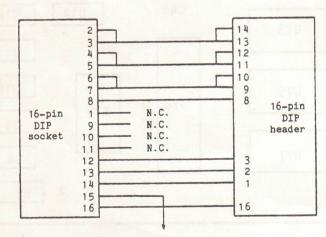
The way to get around this is to mount the '145 in a 16 pin dip socket which is in

turn connected to a 16 pin dip header. However, rather than matching the pins number for number, the connection diagram in Figure 1 is followed. This is most easily accomplished by using a three level wire-wrap socket and cutting short all the pins except 8 and 16. These shortened pins are then wired to the correct position on the header by soldering jumpers on. This causes the pin out connections to be changed and thus allows the '145 to operate in the socket which was previously loaded with the '138.

The 16 pin dip header is then loaded into the MP board into socket U4 as shown in Figure 2. The '145 has the advantage of having four address input lines. Thus address lines A12, A13, A14, and A15 are brought into it and fully decoded. Since address line A12 is not brought to socket U4, it must be separately wired. A convenient place to make this connection is on the MP expansion connector pin #E-R.

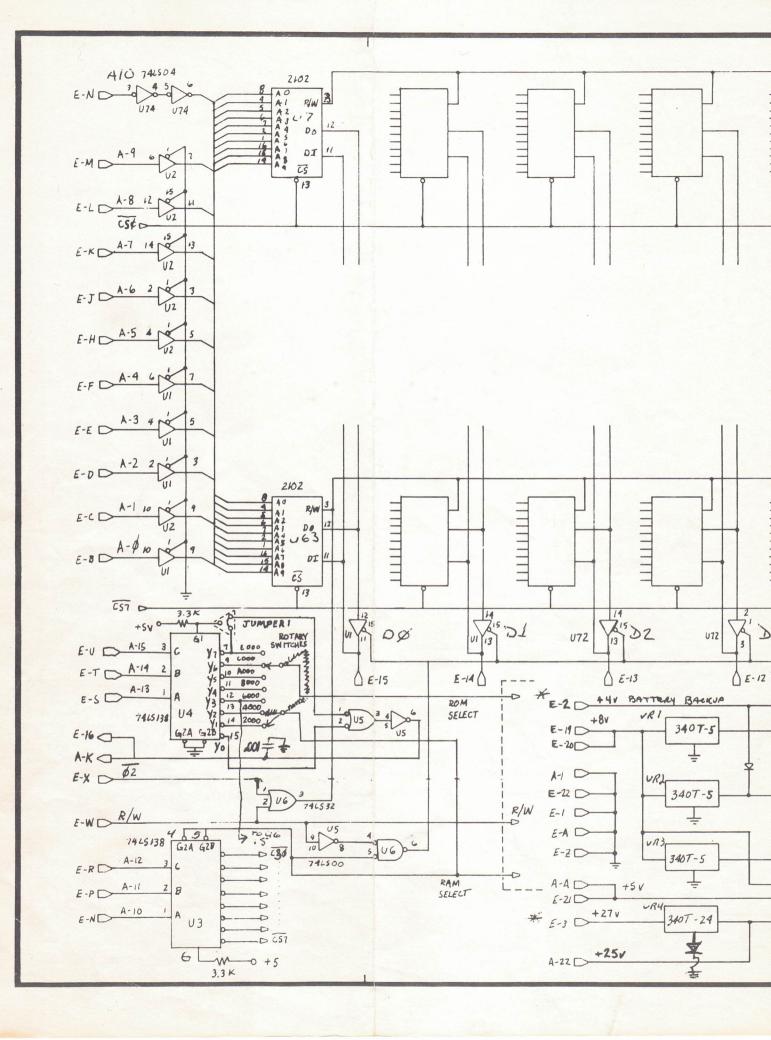
With these changes, the RAM select rotary switch now selects hex locations 1000-2FFF at the first two positions. At the second two positions RAM is selected at 3000-4FFF. In the third two positions RAM is selected at locations 5000-6FFF. RAM will not be selected with the selector switch in the seventh position.

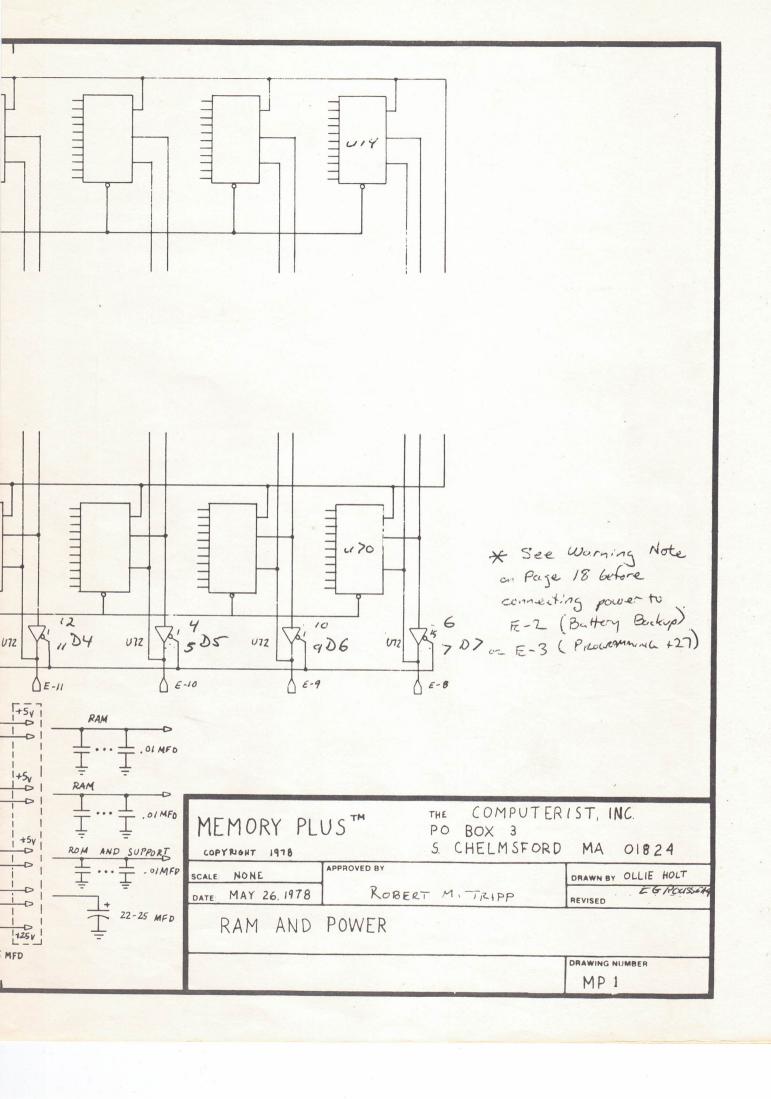
With the switch in the first or second position, BASIC on the SYM can be implemented with 12K memory; the 4K onboard, plus the 8K from the MP. The addition of another MP board set up the same way with the RAM selection switch in either position 3 or 4 would yield a system with 20K of continuous memory.

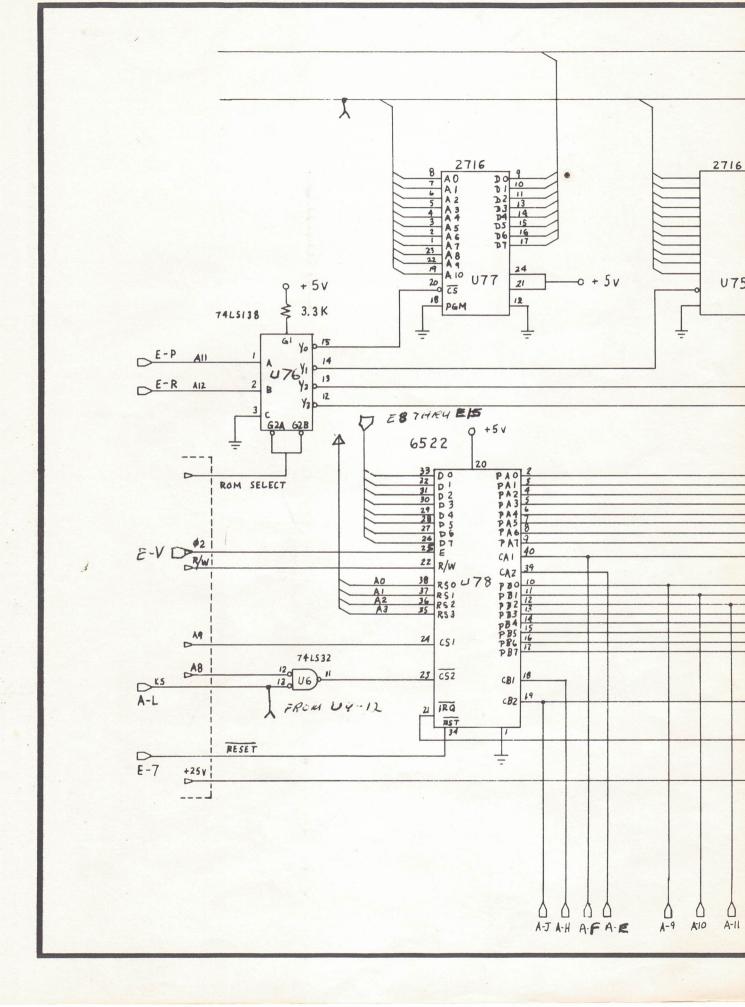


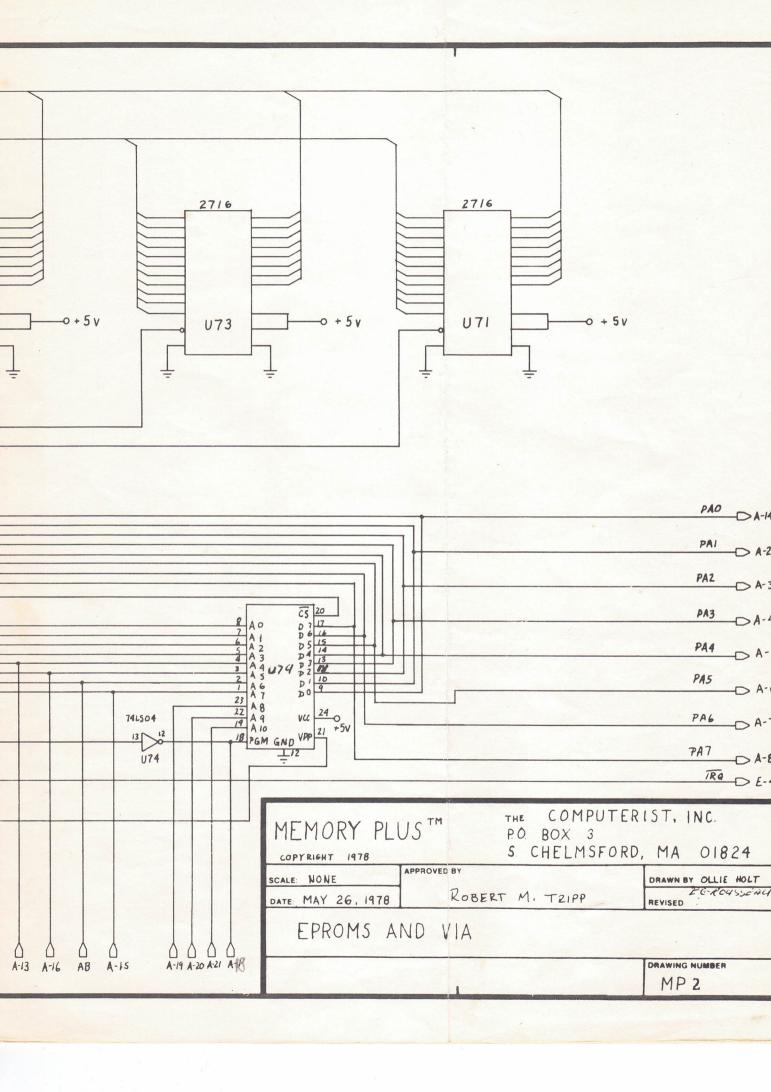
Solder to pin #E-R on the Memory Plus Expansion Connector

Figure 1













2716* 16K (2K × 8) UV ERASABLE PROM

- Fast Access Time
 - 350 ns Max. 2716-1
 - 390 ns Max. 2716-2
 - 450 ns Max. 2716
- Single + 5V Power Supply
- **Low Power Dissipation**
 - 525 mW Max. Active Power
 - 132 mW Max. Standby Power

- Pin Compatible to Intel® 5V ROMs (2316E, 2332, and 2364) and 2732 EPROM
- Simple Programming Requirements Single Location Programming Programs with One 50 ms Pulse
- Inputs and Outputs TTL Compatible during Read and Program
- **■** Completely Static

The Intel® 2716 is a 16,384-bit ultraviolet erasable and electrically programmable read-only memory (EPROM). The 2716 operates from a single 5-volt power supply, has a static standby mode, and features fast single address location programming. It makes designing with EPROMs faster, easier and more economical. For production quantities, the 2716 user can convert rapidly to Intel's pin-for-pin compatible 16K ROM (the 2316E) or the new 32K and 64K ROMs (the 2332 and 2364 respectively).

The 2716, with its single 5-volt supply and with an access time up to 350 ns, is ideal for use with the newer high performance +5V microprocessors such as Intel's 8085 and 8086. The 2716 is also the first EPROM with a static standby mode which reduces the power dissipation without increasing access time. The maximum active power dissipation is 525 mW while the maximum standby power dissipation is only 132 mW, a 75% savings.

The 2716 has the simplest and fastest method yet devised for programming EPROMs — single pulse TTL level programming. No need for high voltage pulsing because all programming controls are handled by TTL signals. Now, it is possible to program on-board, in the system, in the field. Program any location at any time — either individually, sequentially or at random, with the 2716's single address location programming. Total programming time for all 16,384 bits is only 100 seconds.

PIN CONFIGURATION*

	2716				2732					
A7 C	1	5	24	bvcc	A7 [1	V	24 D VCC		
A6 [2		23	□ A8	A6 [2	1	23 A8		
A5 C	3		22	A9	A5 C	3		22 A9		
A4 [4		21	VPP	A4 [4		21 A11		
A3 [5		20	OE	A3 [5		20 OE/VPP		
A2 [6		19	A10	A2 [6		19 A10		
A1 C	7	16K	18	CE	A1 C	7	32K	18 CE		
Ao 🗆	8		17	07	A0 [8		17 07		
00 🗆	9		16	06	00 [9		16 06		
01 [10		15	05	01 [10		15 05		
02	11		14	04	02 [11		14 04		
GND [12		13	03	GND	12		13 03		

†Refer to 2732 data sheet for specifications

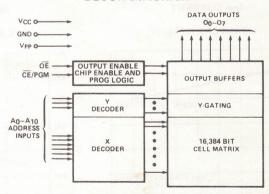
PIN NAMES

A ₀ -A ₉	ADDRESSES
CE/PGM	CHIP ENABLE/PROGRAM
ŌĒ	OUTPUT ENABLE
00-07	OUTPUTS

MODE SELECTION

PINS	CE/PGM (18)	OE (20)	Vpp (21)	VCC (24)	OUTPUTS (9-11, 13-17)
Read	VIL	VIL	+5	+5	DOUT
Standby	VIH	Don't Care	+5	+5	High Z
Program	Pulsed VIL to VIH	VIH	+25	+5	DIN
Program Verify	VIL	VIL	+25	+5	DOUT
Program Inhibit	VIL	VIH	+25	+5	High Z

BLOCK DIAGRAM



*Pin 18 and pin 20 have been renamed to conform with the entire family of 16K, 32K, and 64K EPROMs and ROMs. The die, fabrication process, and specifications remain the same and are totally uneffected by this change.

PROGRAMMING

The programming specifications are described in the Data Catalog PROM/ROM Programming Insutrctions on Page 4-83.

Absolute Maximum Ratings*

Temperature Under Bias ... -10°C to +80°C
Storage Temperature ... -65°C to +125°C
All Input or Output Voltages with
Respect to Ground ... +6V to -0.3V
V_{PP} Supply Voltage with Respect
to Ground During Program ... +26.5V to -0.3V

*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC and AC Operating Conditions During Read

with One 50 ms Puls	2716	2716-1	2716-2
Temperature Range	0°C - 70°C	0°C - 70°C	0°C - 70°C
V _{CC} Power Supply [1,2]	5V ± 5%	5.V ± 10%	5V ± 5%
V _{PP} Power Supply ^[2]	V _{CC} ± 0.6V ^[3]	V _{CC} ± 0.6V ^[3]	V _{CC} ± 0.6V ^[3]

READ OPERATION

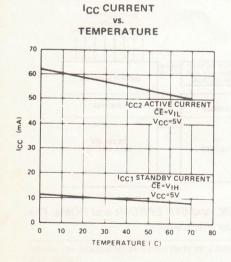
D.C. and Operating Characteristics

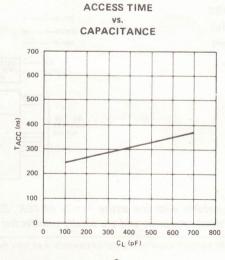
Symbol	Mich. For production contribute, the 27 h.	a bar an	Limits	N (1888) F	BILLIAN .	ист, в экралю ченьки 1	
Symbol	Parameter	Min.	Typ.[4]	Max.	Unit	Conditions	
I _{LI}	Input Load Current	in an esc	mik tzeces	10	μА	V _{IN} = 5.25V	
ILO	Output Leakage Current	Q.5. 11 O.1	3 911 00	10	μΑ	V _{OUT} = 5.25V	
I _{PP1} ^[2]	V _{PP} Current	- Refly	2 3 8 7 3 SI	5	mA	V _{PP} = 5.85V	
I _{CC1} ^[2]	V _{CC} Current (Standby)	ata igom	10	25	mA	CE = V _{IH} , OE = V _{IL}	
I _{CC2} [2]	V _{CC} Current (Active)	AND YES	57	100	mA	OE = CE = V _{IL}	
V _{IL}	Input Low Voltage	-0.1	HENDON ES	0.8	V	THE WITH SERVICE STORY CO.	
V _{IH}	Input High Voltage	2.0		V _{CC} +1	V	SOLUS INCIDENTAL SAFE	
VoL	Output Low Voltage			0.45	V	I _{OL} = 2.1 mA	
V _{OH}	Output High Voltage	2.4			V	Ι _{ΟΗ} = -400 μΑ	

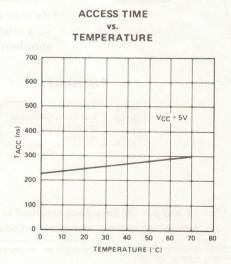
NOTES: 1. VCC must be applied simultaneously or before Vpp and removed simultaneously or after Vpp.

- 2. Vpp may be connected directly to VCC except during programming. The supply current would then be the sum of ICC and IPP1.
- 3. The tolerance of 0.6V allows the use of a driver circuit for switching the Vpp supply pin from VCC in read to 25V for programming.
- 4. Typical values are for TA = 25°C and nominal supply voltages.
- 5. This parameter is only sampled and is not 100% tested.

Typical Characteristics







A.C. Characteristics

Symbol		2716 Limits		2716-1 Limits		2716-2 Limits			Unit	Test		
	Parameter		Тур [4]	Max	Min	Тур [4]	Max	Min	Тур ^[4]	Max	97	Conditions
tACC	Address to Output Delay			450			350			390	ns	CE = OE = VIL
tCE	CE to Output Delay	DI A	الرينا الدو	450		19 Pa	350	N		390	ns	OE = VIL
tOE	Output Enable to Output Delay	TA	DA D	120		3	120			120	ns	CE = VIL
tDF	Output Enable High to Output Float	0		100	0		100	0		100	ns	CE = VIL
tOH	Address to Output Hold	0	301		0			0			ns	CE = OE = VIL

Capacitance^[5] T_A = 25°C, f = 1 MHz

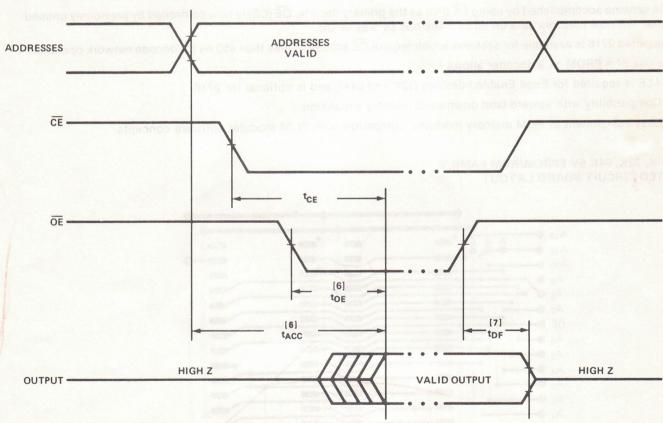
Symbol	Symbol Parameter		Max.	Unit	Conditions		
CIN	Input Capacitance	4	6	pF	V _{IN} = 0V		
C _{OUT}	Output Capacitance	8	12	pF	V _{OUT} = 0V		

A.C. Test Conditions:

Output Load: 1 TTL gate and C_L = 100 pF Input Rise and Fall Times: ≤20 ns Input Pulse Levels: 0.8V to 2.2V Timing Measurement Reference Level:

Inputs 1V and 2V Outputs 0.8V and 2V

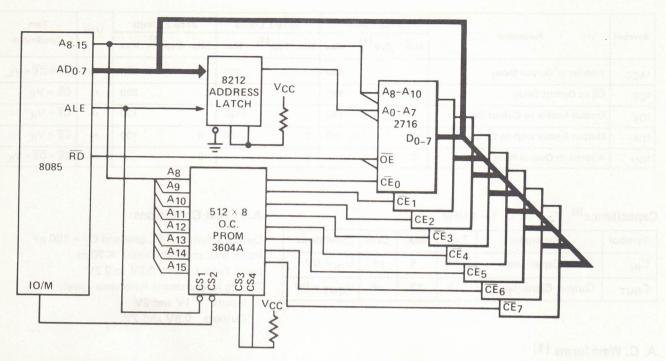
A. C. Waveforms (1)



NOTE: 1. VCC must be applied simultaneously or before Vpp and removed simultaneously or after Vpp.

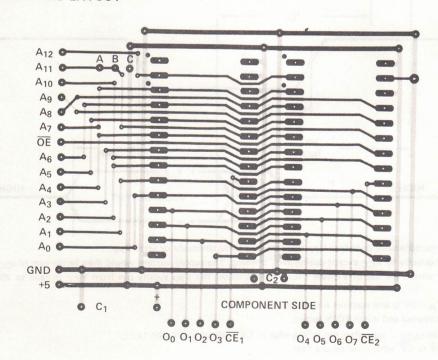
- 2. Vpp may be connected directly to V_{CC} except during programming. The supply current would then be the sum of I_{CC} and I_{PP1}.
- 3. The tolerance of 0.6V allows the use of a driver circuit for switching the Vpp supply pin from V_{CC} in read to 25V for programming.
- 4. Typical values are for TA = 25°C and nominal supply voltages.
- 5. This parameter is only sampled and is not 100% tested.
- 6. $\overline{\text{OE}}$ may be delayed up to $t_{ACC}-t_{OE}$ after the falling edge of $\overline{\text{CE}}$ without impact on t_{ACC} .
- 7. tDF is specified from OE or CE, whichever occurs first.

TYPICAL 16K EPROM SYSTEM



- This scheme accomplished by using CE (PD) as the primary decode. OE (CS) is now controlled by previously unused signal. RD now controls data on and off the bus by way of OE.
- A selected 2716 is available for systems which require CE access of less than 450 ns for decode network operation.
- The use of a PROM as a decoder allows for:
 - a) ALE is required for Edge Enabled devices (32K and 64K), and is optional for 2716.
 - b) Compatibility with upward (and downward) memory expansion.
 - c) Easy assignment of ROM memory modules, compatible with PL/M modular software concepts.

8K, 16K, 32K, 64K 5V EPROM/ROM FAMILY PRINTED CIRCUIT BOARD LAYOUT



ERASURE CHARACTERISTICS

The erasure characteristics of the 2716 are such that erasure begins to occur when exposed to light with wavelengths shorter than approximately 4000 Angstroms (Å). It should be noted that sunlight and certain types of fluorescent lamps have wavelengths in the 3000–4000Å range. Data show that constant exposure to room level fluorescent lighting could erase the typical 2716 in approximately 3 years, while it would take approximately 1 week to cause erasure when exposed to direct sunlight. If the 2716 is to be exposed to these types of lighting conditions for extended periods of time, opaque labels are available from Intel which should be placed over the 2716 window to prevent unintentional erasure.

The recommended erasure procedure (see Data Catalog page 4-83) for the 2716 is exposure to shortwave ultraviolet light which has a wavelength of 2537 Angstroms (Å). The integrated dose (i.e., UV intensity \times exposure time) for erasure should be a minimum of 15 W-sec/cm². The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with a 12000 $\mu \text{W/cm}^2$ power rating. The 2716 should be placed within 1 inch of the lamp tubes during erasure. Some lamps have a filter on their tubes which should be removed before erasure.

DEVICE OPERATION

The five modes of operation of the 2716 are listed in Table I. It should be noted that all inputs for the five modes are at TTL levels. The power supplies required are a +5V V_{CC} and a V_{PP} . The V_{PP} power supply must be at 25V during the three programming modes, and must be at 5V in the other two modes.

TABLE I. MODE SELECTION

PINS	CE/PGM (18)	OE (20)	V _{PP} (21)	VCC (24)	OUTPUTS (9-11, 13-17)
Read	٧IL	VIL	+5	+5	DOUT
Standby	VIH	Don't Care	+5	+5	High Z
Program	Pulsed VIL to VIH	VIH	+25	+5	DIN
Program Verify	VIL	VIL	+25	+5	DOUT
Program Inhibit	VIL	VIH	+25	+5	High Z

READ MODE

The 2716 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (\overline{CE}) is the power control and should be used for device selection. Output Enable (\overline{OE}) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to the delay from \overline{CE} to output (t_{CE}). Data is available at the outputs 120 ns (t_{OE}) after the falling edge of \overline{OE} , assuming that \overline{CE} has been low and addresses have been stable for at least $t_{ACC}-t_{OE}$.

STANDBY MODE

The 2716 has a standby mode which reduces the active power dissipation by 75%, from 525 mW to 132 mW. The 2716 is placed in the standby mode by applying a TTL high

signal to the $\overline{\text{CE}}$ input. When in standby mode, the outputs are in a high impedence state, independent of the $\overline{\text{OE}}$ input.

OUTPUT DESELECTION

The outputs of two or more 2716s may be OR-tied together on the same data bus. Only one 2716 should have its output selected (\overline{OE} low) to prevent data bus contention between 2716s in this configuration. The outputs of the other 2716s should be deselected by raising the \overline{OE} input to a TTL high level.

PROGRAMMING

Initially, and after each erasure, all bits of the 2716 are in the "1" state. Data is introduced by selectively programming "0's" into the desired bit locations. Although only "0's" will be programmed, both "1's" and "0's" can be presented in the data word. The only way to change a "0" to a "1" is by ultraviolet light erasure.

The 2716 is in the programming mode when the V_{PP} power supply is at 25V and \overline{OE} is at V_{IH} . The data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL.

When the address and data are stable, a 50 msec, active high, TTL program pulse is applied to the $\overline{\text{CE}}/\text{PGM}$ input. A program pulse must be applied at each address location to be programmed. You can program any location at any time — either individually, sequentially, or at random. The program pulse has a maximum width of 55 msec. The 2716 must not be programmed with a DC signal applied to the $\overline{\text{CE}}/\text{PGM}$ input.

Programming of multiple 2716s in parallel with the same data can be easily accomplished due to the simplicity of the programming requirements. Like inputs of the paralleled 2716s may be connected together when they are programmed with the same data. A high level TTL pulse applied to the CE/PGM input programs the paralleled 2716s.

PROGRAM INHIBIT

Programming of multiple 2716s in parallel with different data is also easily accomplished. Except for $\overline{\text{CE}}/\text{PGM}$, all like inputs (including $\overline{\text{OE}}$) of the parallel 2716s may be common. A TTL level program pulse applied to a 2716's $\overline{\text{CE}}/\text{PGM}$ input with V_{PP} at 25V will program that 2716. A low level $\overline{\text{CE}}/\text{PGM}$ input inhibits the other 2716 from being programmed.

PROGRAM VERIFY

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify may be performed wth V_{PP} at 25V. Except during programming and program verify, V_{PP} must be at 5V.



Santa Clara, California 95051 Tel: (408) 987-8080 ** TWX: 910-338-0026 TELEX: 34-6372

MICROCOMPUTER AND MEMORY COMPONENT SALES AND MARKETING OFFICES

U.S. AND CANADIAN SALES OFFICES

ALABAMA Glen White Associates 7844 Horseshoe Trail Huntsville 35802 Tel: (205) 883-9394

ARIZONA

Intel Corp. 8650 N. 35th Avenue Phoenix 85021 Tel: (602) 242-7205

CALIFORNIA

Intel Corp. 15335 Morrison Suite 345 Sherman Oaks 91403 (213) 986-9510 TWX: 910-495-2045 Intel Corp.*
990 E. Arques Ave.
Suite 112

Suite 112 Sunnyvale 94086 Tel: (408) 738-3870 TWX: 910-339-9279 TWX: 910-338-0255

Mac-I 2576 Shattuck Suite 4B Berkeley 94704 Tel: (415) 843-7625

Mac-I P.O. Box 1420 Cupertino 95014 Tel: (408) 257-9880 Earle Associates, Inc 4805 Mercury Street Suite L San Diego 92111 Tel: (714) 278-5441 TWX: 910-335-1585

TWX: 910-335-1585 Mac-I P.O. Box 8763 Fountain Valley 92708 Tel: (714) 839-3341 Intel Corp.* 1651 East 4th Street

Suite 150 Santa Ana 92701 Tel: (714) 835-9642 TWX: 910-595-1114

COLORADO Intel Corp. 6000 East Evans Ave Bldg. 1, Suite 260 Denver 80222 Tel: (303) 758-8086 TWX: 910-931-2289 CONNECTICUT

Intel Corp.
Peacock Alley
1 Padanaram Road, Suite 146
Danbury 06810
Tel: (203) 792-8366
TWX: 710-456-1199

FLORIDA

Intel Corp. 1001 N.W. 62nd Street, Suite 406 Ft. Lauderdale 33309 Tel: (305) 771-0600 TWX: 510-956-9407 TWX: 510-936-9407 Intel Corp. 5151 Adanson Street, Suite 105 Orlando 32804 Tel: (305) 628-2393 TWX: 810-853-9219

ILLINOIS . Intel Corp.* 1000 Jorie Boulevard Suite 224 Suite 224 Oakbrook 60521 Tel: (312) 325-9510 TWX: 910-651-5881

TWX: 910-651-5881

INDIANA
Electro Reps Inc.
941 E. 86th Street
Indianapolis 46240
Tel: (317) 255-4147
TWX: 810-341-3217
Electro Reps Inc.
810 Valley-0-Pines Pkwy.
Ft. Wayne 46825
Tel: (219) 637-6211

IOWA
Technical Representatives, Inc.
St. Andrews Building
1930 St. Andrews Drive N.E.
Cedar Rapids 52402
Tel: (319) 393-5510

KANSAS
Technical Representatives, Inc. 8245 Nieman Road, Suite =100 Lenexa 66214
Tel: (913) 888-0212, 3, & 4
TWX: 910-749-6412

MARYLAND Glen White Associates 57 West Timonium Road Timonium 21093 Tel: (301) 252-6360 Intel Corp.*
57 West Timonium Road Suite 307
Timonium 21093
Tel: (301).252-7742
TWX: 710-232-1807

MASSACHUSETTS

Intel Corp.* 187 Billerica Road, Suite 14A Chelmstord 01824 Tel: (617) 256-6567 TWX: 710-343-6333

MICHIGAN Intel Corp. 26500 Northwestern Hwy. Suite 401 Southfield 48075 Tel: (313) 353-0920 TWX: 910-420-1212 TELEX: 2 31143

MINNESO! A Intel Corp. 8200 Normandale Avenue Suite 422 Bloomington 55437 Tel: (612) 835-6722 TWX: 910-576-2867

MISSOURI
Technical Representatives, Inc.
Trade Center Bldg.
300 Brookes Drive, Suite 108
Hazelwood 63042
Tel: (314) 731-5200
TWX: 910-762-0618

NEW JERSEY Intel Corp. 2 Kilmer Road Edison 08817 Tel: (201) 985-9100 TWX: 710-480-6238

IWX: 710-480-6238

NEW YORK
Intel Corp.*
Intel Corp.*
Suite 40:2
Hauppauge 11787
Tel. (516) 231-3300
TWX: 510-227-6236
Intel Corp.
474 Thurston Road
Rochester, N.Y. 14619
Tel. (716) 282-7340
TWX: 510-253-3841
T-Spuared T-Squared 4054 Newcourt Ave. Syracuse 13206 Tel: (315) 463-8592 TWX: 710 541-0554

NEW YORK (cont.) Intel Corp. 85 Market Street Poughkeepsie, New York 12601 Tel: (914) 473-2303 TWX: 510-248-0060

NORTH CAROLINA Glen White Associates 3700 Computer Dr., Suite 330 Raleigh 27609 Tel: (919) 787-7016

OHIO
Intel Corp. *
8312 North Main Street
Dayton 45415
Tel: (513) 890-5350
TELEX: 288-004 Intel Corp.* Chagrin-Brainard Bldg. 28001 Chagrin Blvd. Cleveland 44122 Tel: (216) 464-2736

OREGON ES/Chase Company 7100 S.W. Hampton Street Suite 121 Portland 97223 Tel: (503) 620-9616

PENNSYLVANIA Intel Corp.* 520 Pennsylvania Ave. Fort Washington 19034 Tel: (215) 542-9444 TWX: 510-661-2077

TENNESSE Glen White Associates Rt. =12, Norwood S/D Jonesboro 37659 Tel: (615) 477-8850 Glen White Associates 2523 Howard Road Germantown 38138 Tel: (901) 754-0483 Glen White Associates 6446 Ridge Lake Road Hixon 37343 Tel: (615) 842-7799

TEXAS Intel Corp. 6776 S.W. Freeway Suite 550 Houston 77074 Tel: (713) 784-3400 Mycrosystems Marketing Inc. 13777 N. Central Expressway Suite 405 Dallas 75243 Tel. (214) 238-7157 TWX: 910-867-4763 TWX. 910-867-4763 Mycrosystems Marketing Inc. 6510 Harwin Avenue, Suite 125 Houston 7703-6 Houston 7703-2900 Intel Corp. 2925 L.B.J. Freeway Suite 100 Dallas 7243 Tel V(2) 241-9521 TWX. 910-860-5487

VIRGINIA VIRGINIA
Glen White Associates
P.O. Box 1104
Lynchburg 24505
Tel: (804) 384-6920
Glen White Associates
Rt. = 1, Box 322
Colonial Beach 22443
Tel: (804) 224-4871

WASHINGTON E.S./Chase Co. P.O. Box 80903 Seattle 98108 Tel: (206) 762-4824 Twx: 910-444-2298

CANADA Intel Corp. 70 Chamberlain Ave. Ottawa, Ontario K1S 1V9 Tel: (613) 232-8576 TELEX: 053-4419 Multitek, Inc.*
15 Grenfell Crescent
Ottawa, Ontario K2G 0G3
Tel: (613) 825-4553
TELEX: 053-4585

EUROPEAN MARKETING OFFICES

BELGIUM
Intel International*
Rue du Moulin à Papier
51-Boite 1
B-1160 Brussels
Tel: (02) 660 30 10
TELEX: 24814

Intel Corporation, S.A.R.L.*
74. Rue D'Arcueil
Silic 223
94528 Rungis Cedex
Tel: (01) 687 22 21
TELEX: 270475 FRANCE

SCANDINAVIA

TWX: 710 541-0554 T-Squared 642 Kreag Road P.O. Box W Pittsford 14534 Tel: (716) 248-5005 TELEX: 97-8289

SCANDINAVIA
Intel Scandinavia A/S*
Lyngbyvej 32 2nd Floor
DK-2100 Copenhagen East DK-2100 Copenhai Denmark Tel: (01) 18 20 00 TELEX: 19567 Intel Sweden AB* Box 20092 S-16120 Bromma Sweden Sweden Tel: (08) 98 53 90 TELEX: 12261

ENGLAND

ENGLAND
Intel Corporation (U.K.) Ltd.*
Broadfield House
4 Between Towns Road
Cowley, Oxford OX4 3NB
Tel: (0865) 77 14 31
TELEX: 837203 Intel Corporation (U.K.) Ltd. 46-50 Beam Street Nantwich, Cheshire CW5 5LJ Tel: (0270) 62 65 60 TELEX: 36620

KOREA Koram Digital Sam Yung Bldg, #303 71-2 Bukchang - Dong Chung-Ku Seoul 100

GERMANY
Intel Semiconductor GmbH*
Seidistrasse 27
8000 Muenchen 2
Tel. (089) 55.81.41
TELEX. 923.177
Intel Semiconductor GmbH
Abraham Lincoln Strasse 30
5200 Wiesbaden 1
Tel. (0612) 7.4855
TELEX. 04186183
Intel Semiconductor GmbH
Intel Semiconductor GmbH TELEX: 04186183 Intel Semiconductor GmbH Ernsthaldenstrasse 17 D-7000 Stuttgart 80 Tel: (0711) 7351506 TELEX: 7255346 Intel Semiconductor GmbH Wiesenweg 26 D-6272 Niederhausen Tel: (05127) 2314

ORIENT MARKETING OFFICES

OHIEN I MARKETING OF JAPAN Intel Japan Corporation* Flower Hill-Shinmachi East Bldg. 1-29-9. Shimmachi Setagaya-ku Tokyo 154 Tel: (03) 426-9261 TELEX: 781-28426

TAIWAN
Taiwan Automation Co.*
2nd Floor, 224
Nanking East Road
Section 3
Taipei
Tel: (02) 7710940-3
TELEX: 11942 TAIAUTO

INTERNATIONAL DISTRIBUTORS

ARGENTINA

S.I.E.S.A. Av. Pte. Rogue Saenz Pena 1142 9B 1035 Buehos Aires Tel: 35-6784

AUSTRALIA
A. J. Ferguson (Adelaid
44 Prospect Rd.
Prospect 5082
South Australia 17005
Tel: 269-1244
TELEX: 82635 n (Adelaide) PTY, Ltd. TELEX 82635
A J. Ferguson Electronics
34 Herbert Street
West Ryde. N. S.W. 2114
Tel. AC8 269-1244
TELEX 82635
Warburton-Frankie (Sydney) Pty. Ltd.
199 Parramatta Road
Auburn. N.S.W. 2114
Tel. 648-1311, 649-1381
TELEX. WARFRAN AA 22265
Warburton-Frankie Industries Warburton-Frankie Industries (Melbourne) Pty. Ltd. 220 Park Street South Melbourne, Victoria 3205 Tel: 699-4999 TELEX: WARFRAN AA 31370

AUSTRIA
Bacher Elektronische Gerate GmbH
Meidlinger Hauptstrasse 78
A 1120 Vienna
Tel: (0222) 83 63 96
TELEX: (01) 1532

BELGIUM BELGIUM Inelco Belgium S.A. Avenue Val Duchesse, 3 B-1160 Brussels Tel: (02) 660 00 12 TELEX: 25441

**Note *:-w Telephone Number

RS
DENMARK
Lyngso Komponent A/S
OSMMARK
Lyngso Komponent A/S
OSMMARKEN 4
Tel: (01) 67 00 77
TELEX 22990
Scandinavatian Semiconductor
Supply A/S
Supply A/S
Supply A/S
DK-2200 Copenhagen N
Tel: (01) 83 50 90
TELEX 19037

FINLAND
OY Fintronic AB
Loennrotinkatu 35D
SF 00180
Helsinki 18
Tel: (90) 664 451
TELEX: 12426

FRANCE
Tekelec Airtronic
Cite des Bruyeres
Rue Carle Vernet
92310 Sevres
Tel: (1) 027 75 35
TELEX: 250997

GERMANY
Alfred Neye Enatachnik GmbH
Schillerstrasse 14
D-2085 Quickborn-Hamburg
Tel: (04106) 6121
TELEX: 02-13590

TELEX: 02-13590
Electronic 2000 Vertriebs GmbH Neumarkler: Strasse 75
D-8000 Muenchen 80
Tel: (089) 434061
TELEX: 522561
Jermyn GmbH
Postlach 1146
D-6277 Kamberg
Tel: (06434) 6005
TELEX: 44426

HONG KONG China Electronics Sea Bird House, 9th Floor 22-28 Wyndham Street Hong Kong

ISRAEL Fastronics Ltd.* Eastronics Ltd. 11 Rozanis Street P.O. Box 39300 Tel-Aviv Tel: 475151 TELEX: 33638

TELEX 33538

TIALY
Eledra 3S S P A *
Viale Eleveria, 18
20154 Milan.
TELEX: 39332

Fledra 3S S P A *
Via Paolo Gaidano, 141 D
10137 Torino
TEL: (011) 30 97 097 - 30 97 114

Fledra 3S S P A * Via Giuseppe Valmarana, 63 00139 Rome, Italy Tel: (06) 81 27 290 - 81 27 324 TELEX: 63051 Eledra 3S S.P.A.

JAPAN
Pan Electron
No. 1 Higashikata-Machi
Midori-Ku, Yokohamia 226
Tel: (045) 471-8811
TELEX: 781-4773

JAPAN (cont.)
Ryoyo Electric Corp.
Konwa Bidg.
1-12-22. Tsukiji. 1-Chome
Chuo-Ku. Tokyo 104
Tel: (03) 543-7711
Nippon Micro Computer Co. Ltd.
Mutsumi Bidg. 4-5-21 Kojimachi
Chiyoda-ku. Tokyo 102
Tel: (03) 230-0041

NETHERLANDS Inelco Nederland AFD Elektronic Joan Muyskenweg 22 NL-1006 Amsterdam Tel: (020) 934824 TELEX: 14622

NEW ZEALAND W. K. McLean Ltd. 103-5 Felton Matthew Avenue Glenn Innes, Auckland

NORWAY Nordisk Elektronik (Norge) A/S Mustads Vei 1 N-Oslo 2 Tel: (02) 55 38 93 TELEX: 16963

PORTUGAL Lisboa 1 Tel: 119 45 313

SOUTH AFRICA Electronic Building Elements P.O. Box 4609

Barcelona 10 Tel: 301 78 51

SWEDEN Nordisk Electronik AB

Nordisk Electronik AB Fack S-10380 Stockholm 7 Tel: (08) 248340 TELEX: 10547

SWITZERLAND SWITZERLAND
Industrade AG
Gemsenstrasse 2
Postcheck 80 - 21190
CH-8021 Zurich
Tel: (01) 60 22 30
TELEX: 56788

UNITED KINGDOM

Rapid Recall, Ltd. 11-15 Betterton Street Drury Lane London WC2H 9BS Tel: (01) 379-6741 TELEX: 28752 TELEX: 28752 G.E.C. Semiconductors Ltd. East Lane Wembley HA9 7PP Middlesex Tel: (01) 904-9303 TELEX: 923429 Jermyn Industries Vestry Estate Sevenoaks, Kent. Tel: (0732) 50144 TELEX: 95142

*Field Application Location

